

KAZANKOV, S., instruktor-avianodelist (g.Moskva); POCHEPAYEV, V., chempion  
Moskvy po kordovym skorostnym modelyam (g.Moskva); MASHOVETS, S.,  
krushkovets gorodskogo Doma pionerov (g.Moskva); KUMIN, S., krushkovets  
gorodskogo Doma pionerov (g.Moskva)

Preparing for new competitions. Kryn.rod. 11 no.11:3 N '60.

(MIRA 13:10)

(Moscow--Airplanes--Models)

USSR/Physics - Superconductors

FD-3127

*MASHOVETS, T. V.*  
Card 1/2 Pub. 153 - 2/19

Author : Mashovets, T. V.; Ryvkin, S. M.

Title : ~~Influence of heat treatment upon lifetime of non-ground current carriers~~  
in germanium (the kinetics of the formation of defects during heat treatment)

Periodical : Zhur. tekhn. fiz., 25, No 9 (September), 1955, 1530-1543

Abstract : The authors investigated the influence of heat treatment at relative "low" temperatures (400-550°C) upon the lifetime of non-ground current carriers in germanium. The lifetime decreases with increase of temperature and duration of the heat treatment, which is explained by the occurrence of defects that play the role of centers of recombination. On the basis of a study of the kinetics governing the process of the occurrence the authors obtain data on their energy structure. They show that the process governing the occurrence of defects in the investigated region of temperatures differs from the process governing the occurrence of "thermal defects" ordinarily appearing in germanium at higher temperatures. The authors' aim has been to investigate the occurrence during heat treatment of so called thermal traps (recombination centers) and also the nature (i.e. energy structure) of defects associated with these

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traps. They thank D. N. Nasledov for his interest and also V. M. Tuckevich and A. A. Lebedev for preparation of specimens for measurement. Fourteen references, mostly Western.

Institution : --

Submitted : February 28, 1955

MASHOVETS, T. V.

MASHOVETS, T. V.: "The effect of hot working on the life expectancy of non-basic current carriers in germanium." Acad Sci USSR. Leningrad Physicotechnical Inst. Leningrad, 1956. (Dissertation for the Degree of Candidate in Physicomathematical Sciences.)

SO: Knizhnaya Letopis'. No. 26, 1956

**AUTHOR  
TITLE**

MASHOVETS, T.V., RYVKIN, S.M.

PA - 2118

On the Nature of Recombination Centers created in Germanium on the Occasion of Heat Treatment at "Low Temperatures" (O prirode tsentrov rekombinatsii, vznikayushchikh v germanii pri "niskotemperaturnoy" termoebrabotke).

**PERIODICAL**

Zhurnal Tekhn.Fiz., 1957, Vol 27, Nr 2, pp 238-241 (U.S.S.R.)

Reviewed 3/1957

**ABSTRACT**

Received 3/1957  
First reference is made to the authors' work in Zhurn.Tekhn.Fiz., 1955, Vol 25, p 1530 and its results are summarized. It was found that the processes of the creation of thermocenters in Germanium within the range of "higher" and "lower" temperatures differ. It remained unexplained with what (the admixtures or with structural defects) the low temperature thermocenters of recombination investigated by the authors are connected. To find this out was the task of the present work. Above all it was necessary to determine the position of the levels of the low temperature thermocenters of recombination in the energetical scheme of germanium. This was accomplished by investigating the dependence of life on temperature. It may be concluded that the defects, with which the low temperature recombination centers are connected, are copper atoms. The connection between the defects and the copper atoms was checked in the course of a further series. Results obtained for two samples are shown in form of a table. Summary: 1) The low temperature thermocenters of recombination which are created in consequence of heating at 450 - 550°C and of a subsequent hardening, are connected with a copper-lead admixture.

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On the Nature of Recombination Centers created in Germanium on the Occasion of Heat Treatment at "Low Temperatures".

2) In view of the fact that the recombination centers are uniformly distributed within the entire volume of the sample, it must be assumed that a growth of their concentration with temperature is due to the change of the solubility of copper and not to their diffusion from outside.  
3) The center-forming energy  $U_0 \approx 1.5$  eV, which is determined by the dependence of the steady concentrations of the recombination centers on temperature, is an activation energy for the solution process of the copper. 4) The modification process of the solubility of copper is determined by other and minor time constants than the process of copper diffusion. 5) The  $U_0 \approx 2.0$  eV and  $U_1 \approx 3.5$  eV determined in the previous (Zhurn.Tekhn.Fiz.1955, Vol 25, p 1530) work characterize the position of the copper atom in germanium in the state of a solid solution ( $U_0$ ) and outside the solution ( $U_1$ ). It is, by the way, possible that the aforementioned energies characterize just the germanium atom in the internode space and in the node, if it is assumed that, for the formation of a recombination center, the copper atom must occupy a place in the node instead the germanium. (1 illustration)

Physical-Technical Institute of the Academy of Science of the USSR,  
Leningrad.

ASSOCIATION  
PRESENTED BY  
SUBMITTED  
AVAILABLE  
Card 2/2

4. 10. 1956  
Library of Congress.

**AUTHOR:** Mashovets, T. V. 57-28-6-2/34

**TITLE:** On Recombination on Three Levels of Copper Atoms in Germanium in Consideration of the Statistics of Their Being Filled With Electrons (O rekombinatsii na trekh urovnyakh atomov medi v germanii s ucheton statistiki ikh zapolneniya elektronami)

**PERIODICAL:** Zhurnal Tekhnicheskoy Fiziki, 1958, Vol. 28, Nr 6, pp. 1140-1150 (USSR)

**ABSTRACT:** At present two methods of purifying Germanium from copper by means of thermal treatment are known:  
1) By heating the germanium in the presence of some elements in which the solubility of copper is greater than in germanium (Sn, Pb, Au) (references 2 and 3).  
2) By heating by the passage of a current through the germanium sample. In this case the copper is electrolytically removed into the electrodes (references 4 and 5). In the present paper the author experimentally investigated the influence exercised by "ordinary" thermal treatment upon recombination. Summary: 1) On the basis of

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On Recombination on Three Levels of Copper Atoms  
in Germanium in Consideration of the Statistics of  
Their Being Filled With Electrons

57-28-6-2/34

assuming a reciprocal successive filling up of the 3 acceptor levels of the copper admixture in germanium the dependence of the position of the Fermi level  $\mu$  and of the specific resistance  $\rho$  on the concentration of copper  $N_a$  was calculated for a donor concentration of  $N_d =$

$5 \cdot 10^{13} \text{ cm}^{-3}$ . 2) It is assumed that the influence exercised by the thermal treatment of germanium under "usual" conditions is reduced to the increase of the concentration of the substituting copper atoms. 3) It was shown that by comparing the theoretical and experimental dependences of  $\tau = f(N_a)$  6 capture cross sections (3 for electrons and 3 for holes) can in principle be determined on the 3 levels of the copper atoms. As, however, the contribution made by level I towards recombination is small compared to that made by levels II and III, it is found to be possible in practice to determine 4 capture cross sections (for the levels II and III). The best

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On Recombination on Three Levels of Copper Atoms  
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agreement between calculated and experimental dependence  
- ( $N_a$ ) exists in the case of the following values of  
capture cross sections:  $A_{n2} = 1,8 \cdot 10^{-17} \text{ cm}^2$ ,  $A_{n3} =$   
 $= 3,6 \cdot 10^{-17} \text{ cm}^2$ ,  $A_{p2} = 1,8 \cdot 10^{-16} \text{ cm}^2$ ,  $A_{p3} =$   
 $= 3,6 \cdot 10^{-16} \text{ cm}^2$ . The main contribution is made up to  
concentrations of  $N_a = 10^{14} \text{ cm}^{-3}$  by levels III, whereas  
in the case of higher concentrations  $N_a$  recombination  
on the levels II begins to predominate. 4) Besides, the  
utmost limit of the cross section values of electron  
capture can be evaluated by level I, which is found to  
amount to  $10^{-5}$ . Thus it is possible that, in spite of the  
small contribution towards recombination made by level I  
within this domain, there is no considerable difference  
in the orders of magnitude of the capture cross section.  
5) The calculation method employed in this paper can be

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On Recombination on Three Levels of Copper Atoms  
in Germanium in consideration of the Statistics of  
Their Being Filled With Electrons

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used for any admixture provided that each individual atom substituting the germanium atom in the lattice forms several levels in the forbidden zone. The author thanks S. M. Ryvkin and V. Ye. Khartsiyev for their valuable advice and N. Shcherbakova for her assistance in carrying out calculations. There are 5 figures, 3 tables, and 11 references, 5 of which are Soviet.

**ASSOCIATION:** Leningradskiy fiziko-tehnicheskoy institut, AN SSSR  
(Leningrad Physical-Technical Institute, AS USSR)

**SUBMITTED:** October 29, 1957

- |                           |                      |
|---------------------------|----------------------|
| 1. Germanium—Purification | 2. Copper—Separation |
| 3. Electrodes—Performance | 4. Electron capture  |
| 5. Mathematics            |                      |

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~~24(6), 21(8)~~

67393

SOV/181-1-9-11/31

**AUTHORS:**

Vitovskiy, N. A., Mashovets, T. V., Ryvkin, S. M.

**TITLE:**

Determination of the Number of Acceptor Levels of Defects  
Occurring in Germanium Under the Action of Gamma Irradiation

**PERIODICAL:**

Fizika tverdogo tela, 1959, Vol 1, Nr 9, pp 1381 - 138 (USSR)

**ABSTRACT:**

The radiation-induced formation of structural defects stable at room temperature had already been investigated several times, but not all the problems related therewith are as yet solved satisfactorily. The present paper offers a contribution by discussing the possibilities of a complete analysis of the energy levels of the defects and by publishing experimental results concerning the temperature dependence of the Hall coefficient  $R$  of n-type germanium irradiated by  $\text{Co}^{60}$  rays. An analysis of these results permits a precise determination of the number of acceptor levels belonging to one  $\gamma$ -radiative defect. To investigate the temperature dependence of the carrier concentration in the presence of multiple-charged centers, the authors theoretically investigated a level scheme of a defect (Fig 1), with  $n$  in the conduction band considered to be composed of four parts (Fig 2a). In this connection the

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Determination of the Number of Acceptor Levels of Defects Occurring in Germanium Under the Action of Gamma Irradiation

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following was assumed: every defect produced by radiation has 1 acceptor- and  $k$  donor levels; "ordinary" donors (atoms of the V group) and  $M$  defects exist in such a way in germanium with the concentration  $N_d$ , that  $N_d > M$ .  $n_1$ :  $n$  rises weakly in consequence of transitions of electrons from donor levels to the conduction band;  $n_2$ : full ionization of the donor levels,  $n_2 = N_d - M$ ;  $n_3$ : stronger rising of  $n$  in consequence of transitions of electrons from higher defect levels to the conduction band  $n_3 = N_c M e^{-\Delta E_{M1}/2kT}$ ;  $n_4$ : full ionization of the upper levels,  $n_4 = N_d - N(1-1)$ . The temperature dependence of  $n$  can thus be represented by the function  $\lg n = f(\frac{1}{T})$  (theoretically in Fig 2a, experimentally in 2b). A table gives the results of several measuring series. It is found that for  $\gamma$ -induced defects  $l = 4$ , with  $\Delta E_{M1}$  being 0.18 ev. The defect formation cross section was found to be  $\sigma \approx 4.0 \cdot 10^{-27} \text{ cm}^2$ .

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Determination of the Number of Acceptor Levels of Defects SOV/181-1-9-11/21  
Occurring in Germanium Under the Action of Gamma Irradiation

Directives for further investigations are briefly shown.  
Finally, the authors thank B. M. Konovalenko and I.D. Yaroshetskiy for exposure of the samples and Sh. M. Mirianashvili for his assistance in measurements. There are 2 figures, 1 table, and 3 references, 1 of which is Soviet.

ASSOCIATION: Leningradskiy fiziko-tekhnicheskiy institut AN SSSR (Leningrad  
Institute of Physics and Technology of the AS USSR)

SUBMITTED: March 24, 1959

Card 3/3

"  
VITOVSKIY, N.A.; MASHOVETS, T.V.; RYVKIN, S.M.; SONDAYEVSKIY, V.P.

Energy spectrum of defects arising in Ge under the effect of gamma radiation. Fiz. tver. tela 3 no. 3:998-1001 Mr '61.

(Crystals—Defects) (Germanium) (Gamma rays) (MIRA 14:5)

24.7700

S/058/62/000/006/083/136  
A057/A101

AUTHOR: Mashovets, T. V.

TITLE: Investigation of the recombination process in thermocenters in germanium

PERIODICAL: Referativnyy zhurnal, Fizika, no. 6, 1962, 28, abstract 6E233  
(In collection: "Fotoelektr. i optich. yavleniya v poluprovodnikakh", Kiyev, AN USSR, 1959, 138 - 140)

TEXT: A calculation method of the dependence of the position of the Fermi level and of the basic parameters of Ge upon the concentration ( $N_a$ ) of the substituting Cu admixture is presented under consideration of the presence of multiple-charged Cu levels. It is demonstrated how can the theoretical dependence of the Fermi level position and specific resistance upon  $N_a$  be calculated. A method is described for the determination of 6 recombination cross sections (3 for electrons and 3 for holes) on three Cu levels, which is necessary to obtain the theoretical dependence of the life time ( $\tau$ ) on  $N_a$ . According to data obtained by thermal treatment the dependence of  $\tau$  upon  $N_a$  was determined ex-

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Investigation of the...

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A057/A101

perimentally. The comparison of calculated and experimental curves allowed the determination of 4 recombination cross sections related to two upper Cu levels (the contribution of the lower levels to the recombination is negligibly small). The presented method can be used for any substituting admixture with several levels. ✓

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[Abstracter's note: Complete translation]

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S/181/62/004/003/041/045  
B101/B102

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AUTHORS:

Vitovskiy, N. A., Lukirskiy, D. P., Mashovets, T. V., and  
Byvkin, S. M.

TITLE:

Energy spectrum of some impurity atoms in germanium and  
silicon

PERIODICAL:

Fizika tverdogo tela, v. 4, no. 3, 1962, 816 - 818

TEXT: In a previous paper (FTT, 1, 1381, 1959) the authors suggested a method of determining the total number of acceptor (or donor) levels pertaining to one structural defect and lying in the forbidden band of a semiconductor. The method consists in measuring the temperature dependence of the Hall constant in specimens with known ratio of the concentration of the "ordinary" carriers (of the elements of the groups III and V) to the defect concentration. Such measurements were made in gold-doped n-type Ge, copper-doped n-type Ge, and gold-doped p- and n-type Si. Specimens with known impurity concentrations are obtained by diffusion. In the measurement, the concentration  $M$  of the atoms added must be such that  $M_l < N_l$ , or  $M_k < N_k$ , where  $l$  is the number of the acceptor levels,  $k$

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Energy spectrum of some...

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the number of the donor levels,  $N_d$ ,  $N_a$  are the concentrations of the "ordinary" donors or acceptors, respectively. The results (Fig. 1) which show a concentration  $n_0$  of the ordinary donors prior to doping which corresponds to complete ionization, and  $n_2$  after doping indicate that at liquid-nitrogen temperature filling of the ordinary donors (V-group elements) sets in. The concentration which increases with temperature (Ia and IIb) corresponds to the ionization of the uppermost level of the impurity atom and the concentration  $n_1$  (Fig. 1) to the complete emptying of this level. The relation  $l = (n_0 - n_2)/(n_1 - n_2)$  for Cu in Ge is 3.1; for Au in Ge (2 specimens)  $l = 2.8$  and  $l = 3.1$ . With n-type and p-type Si the curves I and II coincide at high temperatures (approximately 500°K) from which it follows that in silicon gold forms one acceptor level ( $l = 1$ ) and one donor level ( $k = 1$ ). The calculated activation energies for the upper acceptor levels of Cu and Au in Ge, and the acceptor and donor levels of Au in Si agree with published data. There are 2 figures and 5 references: 2 Soviet and 3 non-Soviet. The three references to English-language publications read as follows: H. H. Woodbury a. W. W.

Card 2/4

Energy spectrum of some...

S/161/62/004/003/041/045  
B101/B102

Tyler, Phys. Rev., 105, 84, 1957; R. Newman, Phys. Rev., 94, 278, 1954;  
C. B. Collins, R. O. Carlson, a. Gallagher, Phys. Rev., 105, 1168, 1957.

ASSOCIATION: Fiziko-tekhnicheskiy institut im. A. F. Ioffe AN SSSR,  
Leningrad (Physicotechnical Institute imeni A. F. Ioffe  
of the AS USSR, Leningrad)

SUBMITTED: December 30, 1961

Fig. 1. Temperature dependence of the carrier concentration in  
germanium. (a) doped with Cu; (b) doped with Au.

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VITOVSKIY, N.A.; LUKIRSKIY, D.P.; MASHOVETS, T.V.; MYAKOTA, V.I.

Energy spectrum of defects in silicon caused by electron  
irradiation. Fis. tver. tela 4 no.5:1140-1145 My '62.  
(MIRA 15:5)

1. Fiziko-tekhnicheskiy institut imeni A.F. Ioffe AN  
SSSR, Leningrad.

(Silicon crystals--Defects)  
(Radiation)

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S/101/62/004/010/032/063  
B100/B104

24.7600

**AUTHORS:** Vitovskiy, N. A., Mashovets, T. V., and Ryvkin, S. M.

**TITLE:** The energy spectrum of the gamma radiation defects in silicon

**PERIODICAL:** Fizika tverdogo tela, v. 4, no. 10, 1962, 2845-2848

**TEXT:** The temperature dependence of the Hall constant was studied on n- and p-type silicon samples before and after their exposure to  $\text{Co}^{60}$  gamma radiation. Irradiation ( $1.4 \cdot 10^{17}$  quanta/cm<sup>2</sup>;  $1.15 \cdot 10^{18}$  quanta/cm<sup>2</sup>) reduced the conductivity of silicon. The measurements carried out in the range 55-450°K showed, that irradiation gives rise to two levels in the upper half of the forbidden band that are capable of accepting electrons:  $E_c - 0.18$  ev and  $E_c - 0.5$  ev. The production cross-sections of these levels are approximately  $1.4 \cdot 10^{-26}$  cm<sup>2</sup> and  $1.8 \cdot 10^{-27}$  cm<sup>2</sup>, respectively. In the lower half of the forbidden band there was one level ( $E_v + 0.23$  ev) with a production cross-section of about  $1.2 \cdot 10^{-27}$  cm<sup>2</sup>. There are 2 figures and 2 tables.

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The energy spectrum of the gamma...

S/181/62/004/010/032/063  
B108/B104

ASSOCIATION: Fiziko-tekhnicheskii institut im. A. P. Ioffe AN SSSR,  
Leningrad (Physicotechnical Institute imeni A. P. Ioffe  
AS USSR, Leningrad)

SUBMITTED: May 30, 1962

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S/181/62/004/010/033/063  
B102/B112

**AUTHORS:** Vitovskiy, N. A., Mashovets, T. V., and Ryvkin, S. M.

**TITLE:** Determination of the activation energy of impurity center levels and of structural defects in semiconductors

**PERIODICAL:** Fizika tverdogo tela, v. 4, no. 10, 1962, 2849 - 2853

**TEXT:** A study was made of the temperature dependence of the carrier concentration in semiconductors with impurities and defects, the spectra of which are complicated by their being several types of levels. According to measurements  $\log n = f(1/T)$  is, in this case, a complicated curve comprising plateaus of different lengths and sections with different inclinations. The activation energy of all possible levels is calculated to obtain a quantitative theoretical description. For simplicity a semiconductor is considered having two levels in the forbidden band. At absolute zero one of them should be partially filled with electrons, and the other should be filled completely (Fig. 2). The results can then be generalized for an arbitrary number of levels. If, in the entire temperature range the relation  $\Delta E_2 - \Delta E_1 \gg kT$  is valid where  $\Delta E_i$  are the level activation energies,

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then the neutrality condition of the system can be given by

$$N_e^{-\frac{1}{T}} = m_1 - \frac{M_1}{1 + \frac{1}{T} e^{-\frac{\Delta E_1}{T}}} + \frac{M_2}{1 + \frac{1}{T} e^{-\frac{\Delta E_2}{T}}} \quad (1)$$

the solution is

$$n = \frac{m_1 - \frac{1}{T} N_{e,n}}{2} \pm \frac{1}{2} \sqrt{(T_1 N_{e,n} - m_1)^2 + T_1 \Delta N_{e,n} (M_1 + m_1)} \quad (5)$$

$$N_{e,n} \equiv N_e^{-\frac{1}{T}}$$

The curve  $\log n = f(1/T)$  is divided into 6 sections (2 plateaus, 2 sloping and 2 transition sections),  $n$  is calculated for each section and the state density is studied. With the aid of

$$\Delta E_1 = \frac{d \log n}{d \left( \frac{1}{T} \right)} \left[ 1 - \frac{2.3 \cdot 24}{\sqrt{(m_1 - \frac{1}{T} N_{e,n})^2 + T_1 \Delta N_{e,n} (M_1 + m_1)}} \right] - \frac{3}{2} kT \quad (9)$$

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$\Delta E_2$  can be determined experimentally from the high-temperature inclined section, if  $n_1$  and  $(M_2 + n_1)$  in the point  $\gamma_2$   $n_{on2} = n_1$  is determined from

$$n = \sqrt{(m_1 + M_2) \gamma_2 N_{s,n}} = \sqrt{(m_1 + M_2) n_1} \quad (7)$$

and  $d(\log n)/d(1/T)$  is determined from the curve. The statistical weights  $\gamma_1/\gamma_2$  of the levels need not be known but  $\gamma_2$  can be calculated from (7). These relations are valid if  $M_2 \lesssim n_1$ . If  $M_2 \gg n_1$ , then the activation energy can be calculated directly from the inclination of the curve with the aid of

$$\frac{d \lg n}{d(1/T)} = -\frac{1}{2} \left( \frac{\Delta E_1}{k} + \frac{3}{2} T \right) \quad (11).$$

This is calculated for a practical case. Finally, a further possibility is pointed out of calculating  $\Delta E_2$  from the temperature dependence of the carrier density: the curve  $\log(n - n_1) - f(1/T)$  can be constructed and the

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Determination of the...

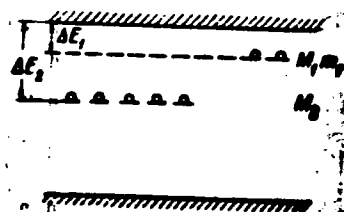
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B102/B112

tangent whose inclination gives the activation energy directly can be drawn at the point corresponding to Eq. (7).  $N_0$  denotes the effective state density in the conduction band,  $M_1$  are the level concentrations and  $n_1$  is the electron concentration on the  $M_1$  level. There are 3 figures.

ASSOCIATION: Fiziko-tekhnicheskiy institut im. A. P. Ioffe AN SSSR, Leningrad (Physicotechnical Institute imeni A. P. Ioffe AS USSR, Leningrad)

SUBMITTED: May 30, 1962

Fig. 2



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E 13899-63 ENP(r)/ENP(n)/BIS APP TO/ASD II

ACCESSION NR: AP3003878 E/0181/63/005/007/1833/1841

AUTHOR: Vitovskiy, N. A.; Konovalenko, B. M.; Machovets, T. V.; Ryskin, S. M.; Yaroshetskiy, I. D.

TITLE: Gamma-ray-generated defects in germanium

SOURCE: Fizika tverdogo tela, v. 5, no. 7, 1963, 1833-1841

TOPIC TAGS: gamma-ray semiconductor irradiation, radiation defect, monopolar annealing, bipolar annealing, germanium irradiation, germanium defect, germanium

ABSTRACT: In the latest stage of research on the subject, dating back to 1959, a large number of n- and p-type specimens was investigated. N-type germanium was doped with antimony and had a donor concentration between  $2 \cdot 10^{12}$  to  $8 \cdot 10^{13}$   $\text{cm}^{-3}$ ; p-type germanium was doped with gallium and had an acceptor concentration between  $10^{13}$  to  $10^{15}$   $\text{cm}^{-3}$ . The source was  $\text{Co}^{60}$  at a dosage of  $2 \cdot 10^{11}$   $\text{kr/cm}^2/\text{sec}$  and temperature of 100. The work was aimed at clarifying the saturation of irradiated specimens which occurs after polarity reversal, whereby further exposure to radiation, however prolonged, no longer affects the slope of the thermal dependence of carrier concentration. The latter remains equal to the activation energy. While the saturation process is evident up to very high concentrations.

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I. 13809-63

ACCESSION NR: AP3003878

of radiation defects, a substantially different situation is obtained in mono-  
polar annealing of interstitial atoms, ultimately leading to a variety of limiting  
states of specimens exposed to gamma radiation. A bipolar annealing effect oc-  
curring during the irradiation process is considered responsible for the drop in  
the defect-formation rate with increased dosage of radiation. Both monopolar and  
bipolar annealing effects were found above room temperature. "The authors are  
indebted to S. R. Novikov for interesting discussions." Orig. art. has: 9 figures

ASSOCIATION: Leningradskiy fiziko-tekhnicheskii institut im. A. F. Ioffe AN SSSR  
(Leningrad Physicotechnical Institute, AN SSSR)

SUBMITTED: 31Jan63

DATE ACQ: 15Aug63

ENCL: 00

SUB CODE: PH

NO REF SOV: 006

OTHER: 003

Card 2/2

VITOVSKIY, N.A.; MASHOVETS, T.V.; RYVKIN, S.M.; KHASEVAROV, R.Yu.

Change of the electric and photoelectric properties of gallium arsenide  
irradiated by 1 Mev. electrons. Fiz. tver. tela 5 no.12:3510-3523 D'63.  
(MIRA 17:2)

1. Fiziko-tekhnicheskii institut imeni A.F.Ioffe AN SSSR, Leningrad.

L 10792-65 ENT(1)/ENG(x)/T Pz-6 IJP(c)/ASD(a)-5/ASD(m)-3/AS(mp)-2/  
 AFNL/ESD(t) AT  
 ACCESSION NR: AP1039649 B/0181/64/006/006/1654/1656

TITLE: A possible method of precise determination of activation energies of  $E$  impurity levels and of defects in semiconductors

SOURCE: Fizika tverdogo tela, v. 6, no. 6, 1964, 1654-1656

TOPIC TAGS: activation energy, impurity level, defect, semiconductor, Hall coefficient

ABSTRACT: The authors suggest a method of determining the activation of impurity levels from nonlinear segments of the temperature dependence of the Hall coefficient. Two arbitrary temperature intervals are selected in which the changes in concentration and the degree to which the level is filled with electrons are known. These values may then be related by a simple equation (they form a simple proportion), and a graphic solution yields the value of the activation energy ( $\Delta E_H$ ). It is then easy to compute the absolute concentration and from this to determine the electron concentration at the desired level. The authors have shown that when

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ACCESSION NR: AP4039619

the conditions

$$\begin{aligned} P_v &= \frac{1}{N} \sum_{i=1}^N \epsilon_{mi} \\ P_v &= \frac{1}{N} \sum_{i=1}^N \epsilon_{mi} \end{aligned}$$

(where  $P_v$  is the effective density of states in the valence band,  $N$  is the concentration of centers belonging to the examined level, and  $n_0$  is the electron concentration at the same level at absolute zero) are not fulfilled, the determination of  $E_v$  by the ordinary method, from the slope of the dependency expression  $\log R = f(1/T)$ , leads to substantial errors. "The authors thank I. D. Yaroshetskiy for his valuable suggestions." Orig. art. has: 1 figure, 1 table, and 7 formulas.

ASSOCIATION: Fiziko-tekhnicheskii institut im. A. F. Ioffe AN SSSR, Leningrad (Physico-technical Institute, AN SSSR)

SUBMITTED: 13 Dec 63

SUB CODE: 94, 68

NO REF SOV: 002

ENCL: 00

OTHER: 002

Card 2/2



L 10521-65 EWP(m)/EPF(c)/EPF(n)-2/EWP(b) Pr-4/Pu-4 IJP(c)/AEDC(a)/  
AS(m)E/ASD(m)-5/AFWL/SSD/ESD(gs)/ESD(a)-5/ESD(c) JD/38

S/0181/64/006/006/1883/1892

ACCESSION NR: AP4039684

AUTHORS: Mitovskiy, N. A.; Mashovets, T. V.; Ryskin, S. M.

TITLE: High-temperature annealing of gamma radiation defects in n-type germanium

SOURCE: Izv. Vsesoyuzn. nauch. ts. fiz. mat. nauch. 6, no. 6, 1964, 1883-1892

TOPIC TERMS: annealing; gamma radiation defects; germanium; defect level; activation energy; high temperature effect

ABSTRACT: The authors measured the temperature dependence of the Hall effect in samples before and after irradiation and at various stages of annealing. Sequential isothermic annealing was carried out on two series of samples containing donor concentrations (antimony) of  $4 \cdot 10^{13}$  and  $2 \cdot 10^{14}$  cm<sup>-3</sup> respectively. Annealing was done in an oil bath at 90, 100, 120, 200, and 300C. Each series included samples irradiated at +100 with different doses of gamma rays from Co<sup>60</sup>. The authors show that the basic process of high-temperature annealing in samples irradiated at room temperature is bipolar annealing of the donor and acceptor components of the gamma-radiation defects. The activation energy of annealing was shown to be the same for the  $E_v - 0.20$  ev and the  $E_v + 0.11$  ev levels ( $1.2 \pm 0.1$  ev). Unipolar annealing occurs along with the bipolar process. The unipolar annealing of donors is always

Cont. 1/2

L 10521-65  
ACCESSION NR: APL039684

relatively more rapid than unipolar annealing of acceptors. Unipolar annealing of acceptors was observed only when such annealing of donors created an excessive concentration of acceptors and when the absolute rate of acceptor annealing exceeded the absolute rate of donor annealing. The authors show that, as a result of high-temperature annealing in gamma-irradiated germanium, two new levels are formed: an  $E_c - 0.13$  ev and an  $E_v + 0.22$  ev. These indicate a reorganization of the radiation defect during annealing. "The authors thank I. P. Shershneva, graduate student at LGU, for making a number of measurements." Orig. art. has: 6 figures, 4 tables, and 1 formula.

ASSOCIATION: Fiziko-tekhnicheskiy institut AN SSSR, Leningrad (Physicotechnical Institute AN SSSR)

SUBMITTED: 13Dec63

ENCL: 00

SUB CODE: PM, TD

NO REF SOV: 009

OTHER: 004

Card : 1/2

L 24165-15 EWT(m)/EPF(c)/EPF(n)-2/EWP(t)/EWP(b) Pr-4/Pu-4 IJP(c)  
 ACCESSION NR: AP5003463 JD/GG S/0181/65/007/001/0308/0310

AUTHOR: Mashovets, T. V.; Khansavapov, R. Yu.

TITLE: Energy structure of gamma-radiation defects in germanium

SOURCE: Fizika tverdogo tela, v. 7, no. 1, 1965, 308-310

TOPIC TAGS: germanium defect, impurity photoconductivity, radiation defect, gamma irradiation, defect level

ABSTRACT: An investigation has been made of the spectral distribution of impurity photoconductivity in specimens containing defects with different charge states and the influence of annealing of irradiated specimens on spectral distribution of photoconductivity. The specimens were cut out from different monocrystals with an initial concentration of donors (antimony) ranging from  $4 \times 10^{13}$  to  $3 \times 10^{16} \text{ cm}^{-3}$ . Irradiation was conducted at 100°. In addition to the spectral dependence of impurity photoconductivity of specimens before irradiation, after irradiation, and after annealing, the dependence of charge-carrier concentration on temperature was obtained. The rate of irradiation of specimens and the temperature of measurements were selected in

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L 24165-65

ACCESSION NR: AP5003463

such a way that the filling of defect levels with electrons was realized as follows: 1) all defect levels located below the levels of chemical donors were filled with electrons; 2) the  $E_c - 0.20$  eV level was partially filled; 3) the  $E_v + 0.27$  eV level was partially filled; 4) the  $E_v + 0.22$  eV level was partially filled; and 5) the  $E_v + 0.11$  eV level was practically filled. Analysis of the energy diagrams showed that the  $E_c - 0.27$  eV,  $E_v + 0.32$  eV, and  $E_v + 0.16$  eV levels are always present in all specimens before irradiation and remain after annealing. It is possible that these levels could be attributed to some constantly present impurities. The  $E_c - 0.20$  eV,  $E_c - 0.34$  eV,  $E_v + 0.27$  eV,  $E_v + 0.22$  eV, and  $E_v + 0.11$  eV levels are produced during irradiation, the last two only during prolonged irradiation. The stability of radiative defects with regard to annealing increases with increasing radiation dose. Orig. art. has: 1 table. [JA]

ASSOCIATION: Fiziko-tekhnicheskiy Institut im. A. F. Ioffe AN SSSR, Leningrad (Physicotechnical Institute, AN SSSR)

E 24165-65

ACCESSION NR: AP5003463

SUBMITTED: 08AUG64

ENCL: 00

SUB CODE: NP,SS

NO REF SOV: 006

OTHER: 002

ATD PRESS: 3175

Card 3/3



L 56010-65 EWT(m)/EFT(o)/EFT(n)-2/EWT(t)/EWP(b) Pr-4/Pu-4 LJP(o) JD/CG  
 ACCESSION NR: AP5017330 13/0181/65/COT/001/2229/2231 32  
 31/8  
 AUTHOR: Mashovets, T. V.; Khansevarov, R. Yu.  
 TITLE: Energy spectrum of defects appearing in indium antimonide at low-temperature  $\gamma$ -irradiation 27 21  
 SOURCE: Fizika tverdogo tela, v. 7, no. 7, 1965, 2229-2231 19  
 TOPIC TAGS: gamma irradiation, irradiation defect, indium antimonide defect, defect formation threshold energy, impurity photoconductivity  
 ABSTRACT: Results are presented of an investigation of the energy spectrum of defects appearing in n-type indium antimonide irradiated with a dose of  $2.4 \times 10^{10}$  quanta/cm<sup>2</sup> of  $\gamma$ -rays from a Co<sup>60</sup> source at 77K. The specific resistance, the concentration of current carriers, and the spectral dependences of impurity photoconductivity were measured on specimens before and after irradiation at 77K. The considerably increased photoconductivity of the specimens in proportion to the irradiation was attributed to the rise in the concentration of radiation defect levels. During irradiation the conductivity changed from n to p type when the specimens passed over the region of total compensation. After the change in conductivity, the hole concentration at first increased, then approached a limiting value.  
 Card 1/2

L 56010-65

ACCESSION NR: AP501/330

The rate of the electron concentration decrease was  $3 \times 10^{-11}$  electron/cm<sup>2</sup>·photon. Discontinuation of the rise of the radiation defect concentration levels was due to an equilibrium between the processes of the generation and annealing of the defects. It is possible 1) that the annealing rate in centers whose  $E_v + 0.038$  eV level is free of electrons is considerably higher than the annealing rate in centers with filled levels, and 2) that the moment of equilibrium establishment between generation and annealing is determined not by the magnitude of concentration of  $E_v + 0.038$  eV levels but by the number of empty places on them. Orig. art. has 2 figures. [JA]

ASSOCIATION: Fiziko-tekhnicheskiy institut im. A. F. Ioffe AN SSSR, Leningrad  
(Physicotechnical Institute, AN SSSR)

SUBMITTED: 15Feb65

ENCL: 00

SUB CODE: N288

NO REF SOV: 001

OTHER: 000

ATD PRESS: 4034

CSC  
Card 2/2

L 32636-66 EWT(m)/EWP(t)/ETI LJP(c) JD/GG  
ACC NR: AP6018527 SOURCE CODE: UR/0181/66/008/006/1690/1697

AUTHOR: Mashovets, T. V.; Khansevarov, R. Yu.

ORG: Physicotechnical Institute im. A. F. Ioffe, AN SSSR, Leningrad (Fiziko-  
tekhnicheskiy institute AN SSSR)

TITLE: Low-temperature gamma irradiation and annealing of indium antimonide

SOURCE: Fizika tverdogo tela, v. 8, no. 6, 1966, 1690-1697

TOPIC TAGS: indium compound, indium antimonide, irradiation, annealing, resistivity,  
Hall constant, photoconductivity, radiation damage, crystal defect

ABSTRACT: In view of the scarcity of published data on the effect of gamma irradiation on InSb, the authors irradiated n-type InSb at 77K (dose rate  $2.4 \times 10^{10}$  photons/cm<sup>2</sup> sec) with initial electron density  $2.9 \times 10^{13}$  -  $1.6 \times 10^{14}$  cm<sup>-3</sup> and p-type InSb with initial hole density  $5.3 \times 10^{13}$  -  $3.3 \times 10^{14}$  cm<sup>-3</sup>. The resistivity, Hall constant, and the spectral distribution of the photoconductivity were measured before and during irradiation, and during the subsequent annealing. The test results are used to determine the rate of defect formation and the extremal positions of the Fermi level as functions of the irradiation dose. The results indicate that the defects produced by irradiation act as ionized scattering centers, and that the rate of defect formation is a rather complicated function of the irradiation dose. Some hypotheses are advanced concerning the energy level scheme of the irradiated indium antimonide. It is concluded that

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L 32636-66

ACC NR: AP6018527

3  
there are several simultaneously acting mechanisms affecting the course of annealing of the radiation defects, and that the rate of this annealing depends on the initial carrier density in the semiconductor. Investigation of the isochronous annealing of defects in the interval 77 — 300K yielded results that agree with published data, thus indicating that these processes are governed by the main defects always produced after irradiation. Two levels,  $E_c - 0.083$  and  $E_v + 0.048$  eV, are credited to radiation defects and are classified as donor and acceptor levels, respectively. The authors thank S. M. Ryvkin for interest, V. V. Galavanov for supplying many samples, and L. V. Nikina for help with the measurements. Orig. art. has: 7 figures and 4 tables.

[02]

SUB CODE: 20/ SUBM DATE: 16Oct65/ ORIG REF: 007 OTH REF: 003/  
ATD PRESS: 5024

Card 2/2 20

MAKHOVETS, V., inzhener.

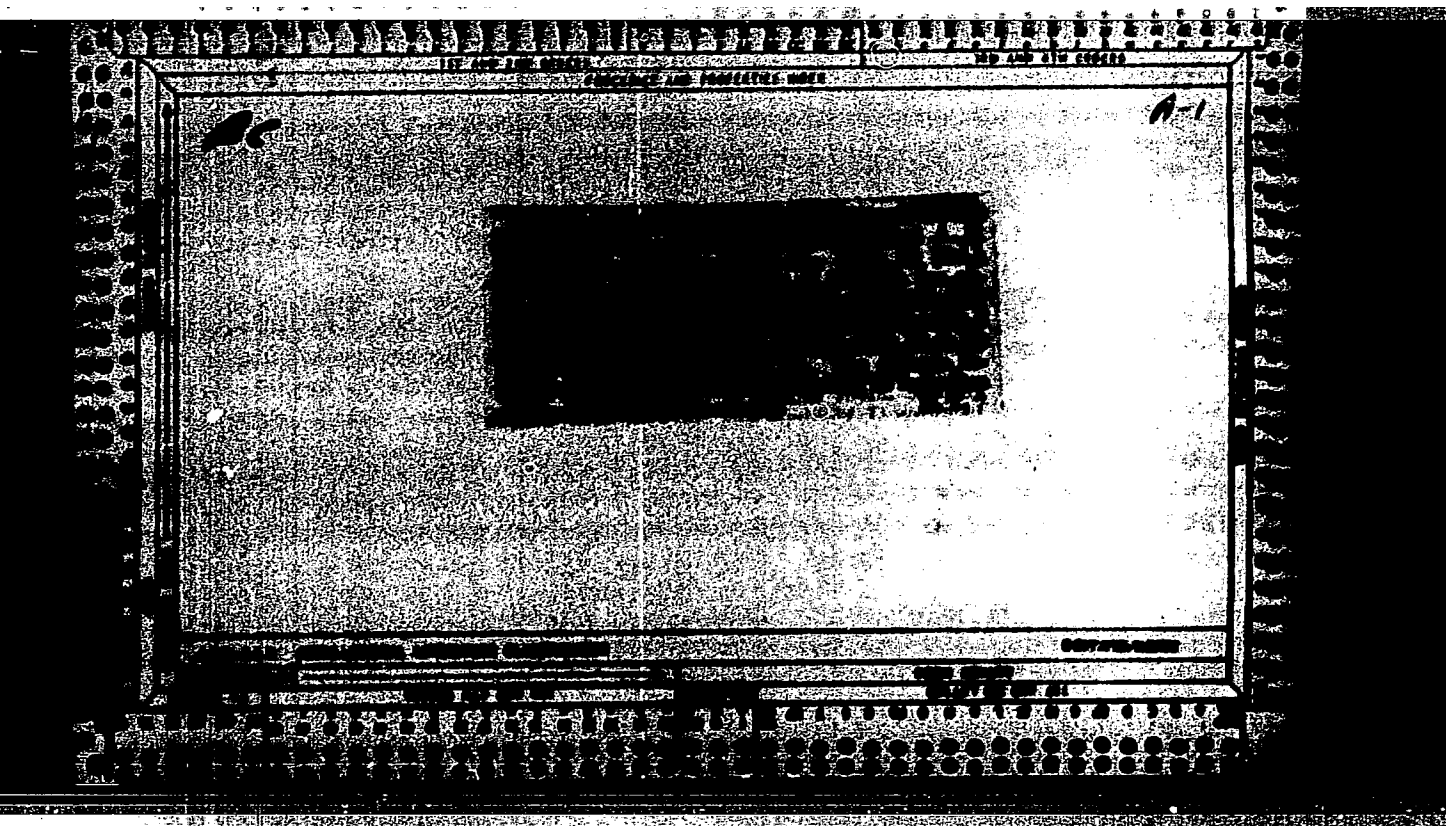
Planning the repair of port cargo-handling installations.  
Mor.flet.15 no.11:7-9 N '55. (MIRA 9:2)

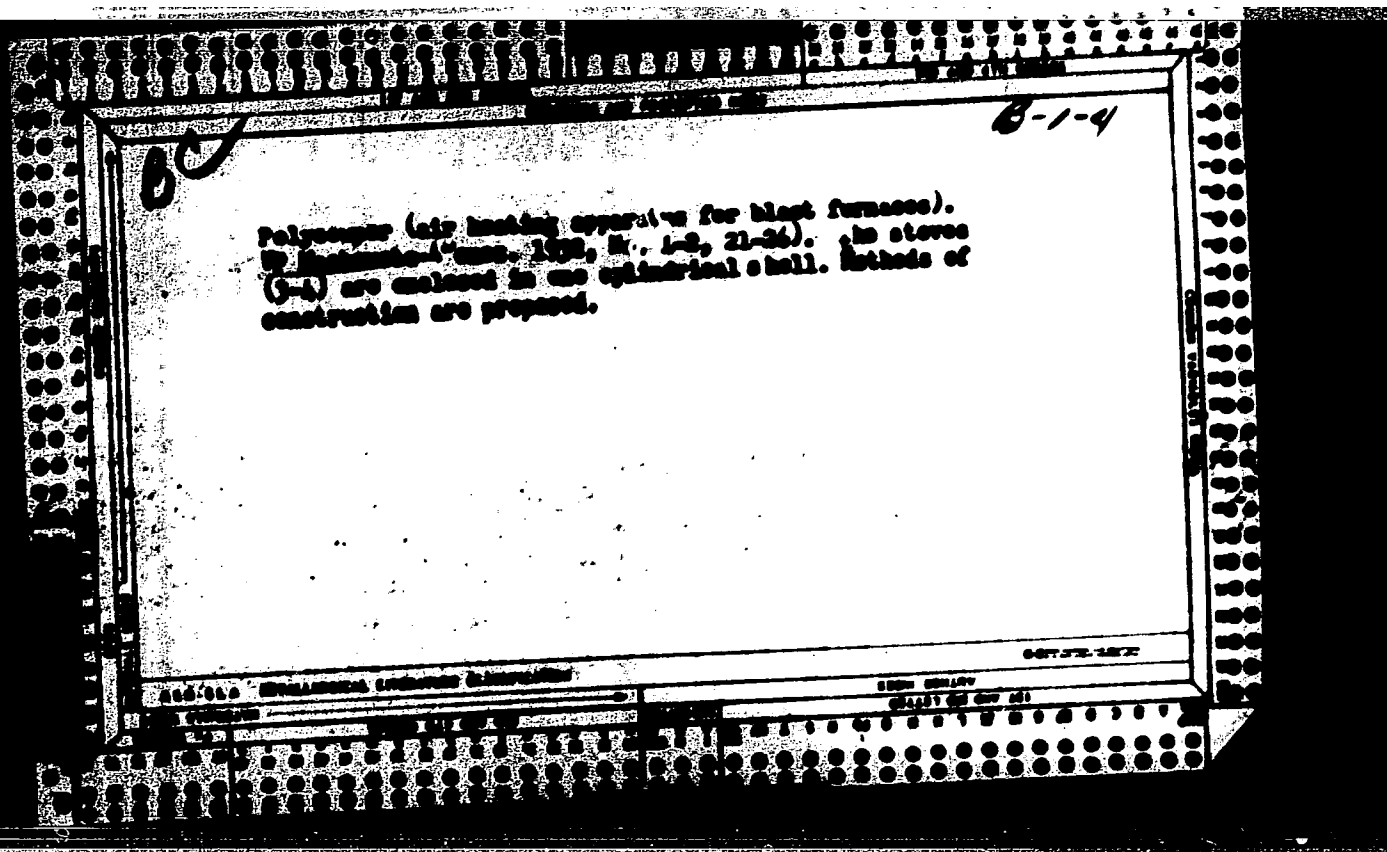
1. Nachal'nik otдела mekhanizatsii Leningradskogo porta.  
(Loading and unloading) (Harbors)

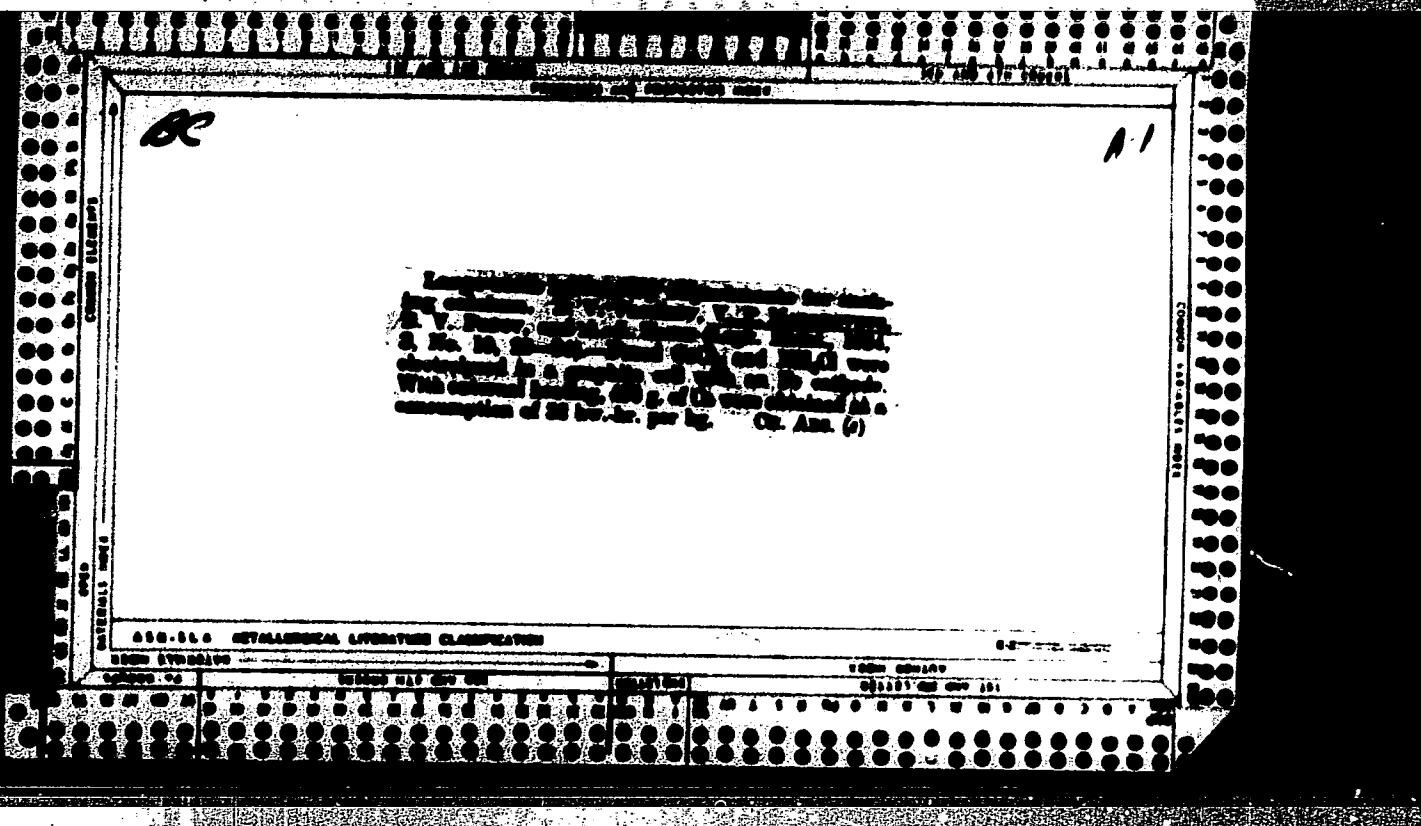
**MASHOVETS, V., inzhener.**

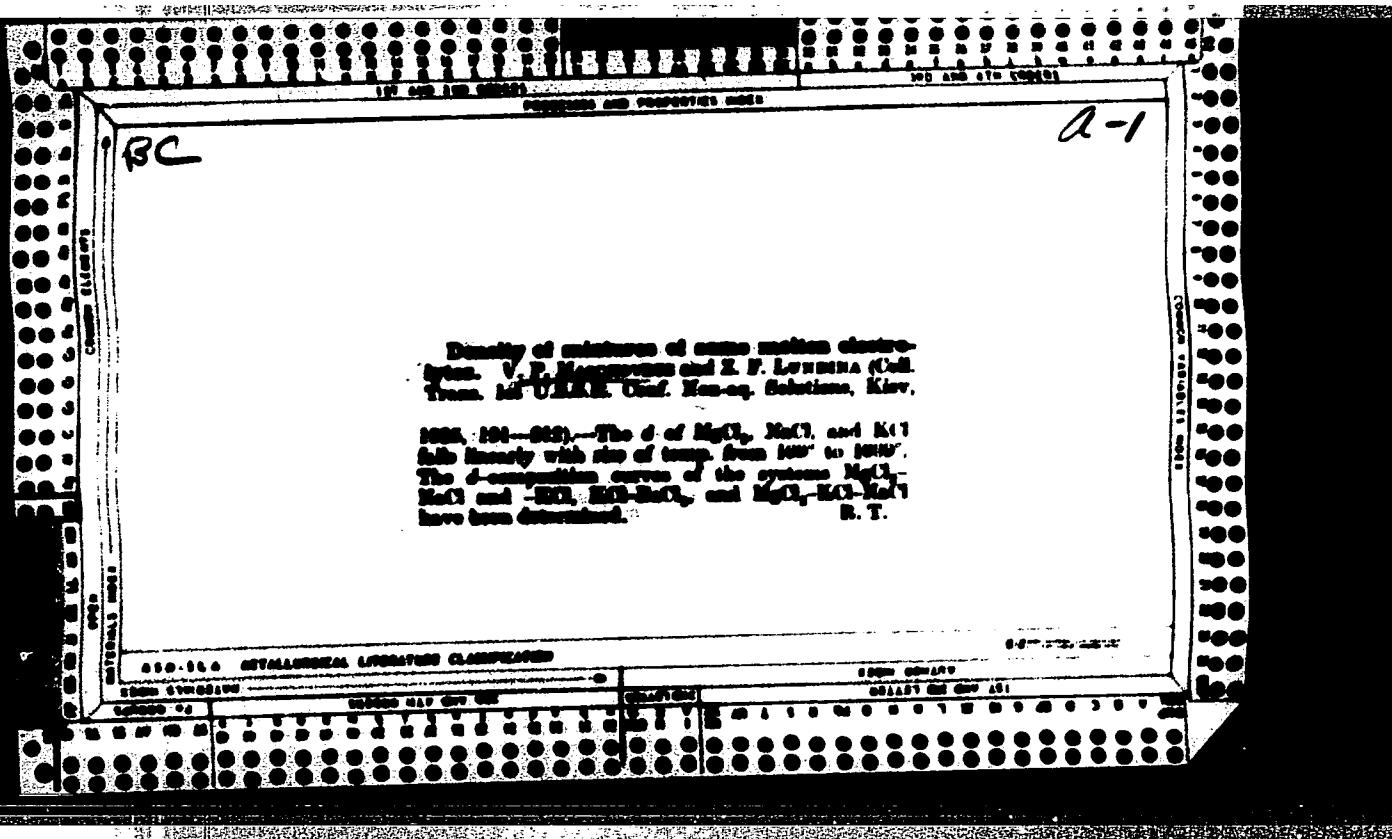
**Better organization for the technical operation of harbor machinery.  
Mer.flet 16 no.5:5-7 My '56. (MLRA 9:8)**

- 1. Partiyaya organizatsiya Tsentral'nogo komiteta Kommunisticheskoy partii Sovetskogo Soyusa Leningradskogo porta.  
(Harbors) (Conveying machinery) (Cargo handling)**









151 AND 152 CDS-181		PROCESS AND PROPERTIES INDEX		160 AND 170 CDS-181	
<p><i>co</i></p> <p>Changes of the melting point and the "degeneration" of cryolite by fusion in air. V. P. Koshovits. <i>J. Applied Chem.</i> (U. S. S. R.) 9, 750-54 (1956) (1956). The conflicting literature data on the results of decomp. of cryolite and the nature of cryolite with <math>Al_2O_3</math> have critically discussed, led to a study of the changes in the chem. compn. and the temp. of incipient crys. of cryolite on prolonged heating. Samples of Greenland and propyl. cryolites were heated in loosely covered Pt crucibles of different diam. in an air Pt furnace at <math>1000^\circ</math> for various periods of time up to 2 hrs. At intervals of about 1 hr. the heating was discontinued, and the temp. of solidification was measured by means of a Pt-Ir thermocouple by the visual method. The results show that with the elapsed heating time the temp. of incipient crys. of cryolite decreases at an increasing rate until a min. is reached, and then rapidly rises. The rate of the decrease varies even for the same specimen, depending on the conditions of crys. and the diam. of the Pt crucible. The analysis of melts at various stages and the changes in the comp. of crys. suggest a thermal "degeneration" of</p>		<p>cryolite on contact with the <math>O_2</math> derived from the atm. or the moisture, with a loss of F and the formation of <math>AlF_3</math>. (1) <math>2Na_2AlF_6 + 1.5O_2 = Al_2O_3 + 6NaF + 3F_2</math>, <math>222.2</math> Cal., or (2) <math>2Na_2AlF_6 + 3H_2O = Al_2O_3 + 6NaF + 6HF</math>, <math>-143.8</math> Cal. The process of degeneration may also be conceived by other reactions with the formation of <math>NaAlO_2</math>: (3) <math>Na_2AlF_6 + O_2 = NaAlO_2 + 2NaF + 2F_2</math>, <math>-223.1</math> Cal., or (4) <math>Na_2AlF_6 + 2H_2O = NaAlO_2 + 2NaF + 4HF</math>, <math>-104.1</math> Cal. The reactions 1 and 3 or 2 and 4 differ only in the distribution of O and F between Al and Na. In their effect on the m. p. they give the same results, because this distribution is detd. by an equil. <math>Na_2AlF_6 + 2Al_2O_3 \rightleftharpoons 3NaAlO_2 + 2AlF_3</math>, or <math>Na_2AlF_6 + 3NaAlO_2 \rightleftharpoons 2Al_2O_3 + 6NaF</math>. The eq. estms. of all samples of degenerated cryolite gave an alk. reaction. The mechanism of thermal degeneration of cryolite was proved by the identity of the temps. of initial crys. of the degenerated cryolite and the synthetic preps. with the compn. of the corresponding degrees of cryolite degeneration. Further proof of the displacement of F by O with the liberation of F or HF, and not that of <math>AlF_3</math>, is furnished by the observation of the excessive destruction of the porcelain parts of the app. (Ardt and Kalass, <i>C. A.</i> 18, 3516). Furthermore, Lundina (not published) observed that no change in the solidification temp. takes place on heating cryolite in a specially constructed hermetically sealed Pt crucible. Phys. chem. studies of cryolite melts should be performed with the exclusion of air or in an atm. of dry inert gas.</p>		<p>E 2</p>	
ASD-55A METALLURGICAL LITERATURE CLASSIFICATION		151 AND 152 CDS-181		160 AND 170 CDS-181	



Twenty-one references. Molecular condition of oxides involved in cryolite. *Ibid.* 112-5 (in English 1115-6). Previously it was shown that a state of equil. exists between CaO and the products of its interaction with cryolite in the melt:  $3\text{CaO} + 2\text{Na}_3\text{AlF}_6 \rightleftharpoons 3\text{CaF}_2 + \text{Al}_2\text{O}_3 + 6\text{NaF}$  (*Trudni Vysokomogo Alum. magnitovogo Inst.* 13, 21 (1935)). A similar equil. with the formation of Ca aluminate is possible:  $4\text{CaO} + 2\text{Na}_3\text{AlF}_6 \rightleftharpoons 3\text{CaF}_2 + \text{Ca}_2\text{Al}_2\text{O}_7 + 6\text{NaF}$ , or  $6\text{CaO} + 2\text{Na}_3\text{AlF}_6 \rightleftharpoons 3\text{CaF}_2 + \text{Ca}_3\text{Al}_2\text{O}_6 + 6\text{NaF}$ . The existence of these equilibria was shown by the identity of the temps. of initial crystn. of the separate melts composed of the components of the left and right part of the equations. Thus a complete analogy exists between the equil. of Na<sub>2</sub>O and cryolite and that of CaO and cryolite. In the case, production is impossible to obtain a state of equil. for Na<sub>2</sub>O or CaO, because during the electrolysis the entire O and the equiv. amt. of Al are eliminated from the cell, while NaF accumulates. Hence the introduction of Na<sub>2</sub>O into the cell is equiv. to the addn. of NaF and Al<sub>2</sub>O<sub>3</sub>. The addn. of Na<sub>2</sub>O or CaO should be compensated by the addn. of Al<sub>2</sub>O<sub>3</sub>, i.e., 1 kg. AlF<sub>3</sub> to 1 kg. CaO, and 1.6 kg. Al<sub>2</sub>O<sub>3</sub> to 1 kg. Na<sub>2</sub>O. The pressure of aluminum in the electrolyte may be explained by the existence of the anion  $\text{AlO}_2^-$ . The const. structure of Al<sub>2</sub>O<sub>3</sub>, deriv. by x-ray analysis (Bruggi, *X-ray Rays and the Structure of Crystals*, Moscow, 1930 (1930)) suggests that alumina exists as  $\text{Al}(\text{AlO}_2)_3$ , which he discovers. (forms  $\text{AlH}_2$ ).  
Chas. B. Shaw

✓ 3 1

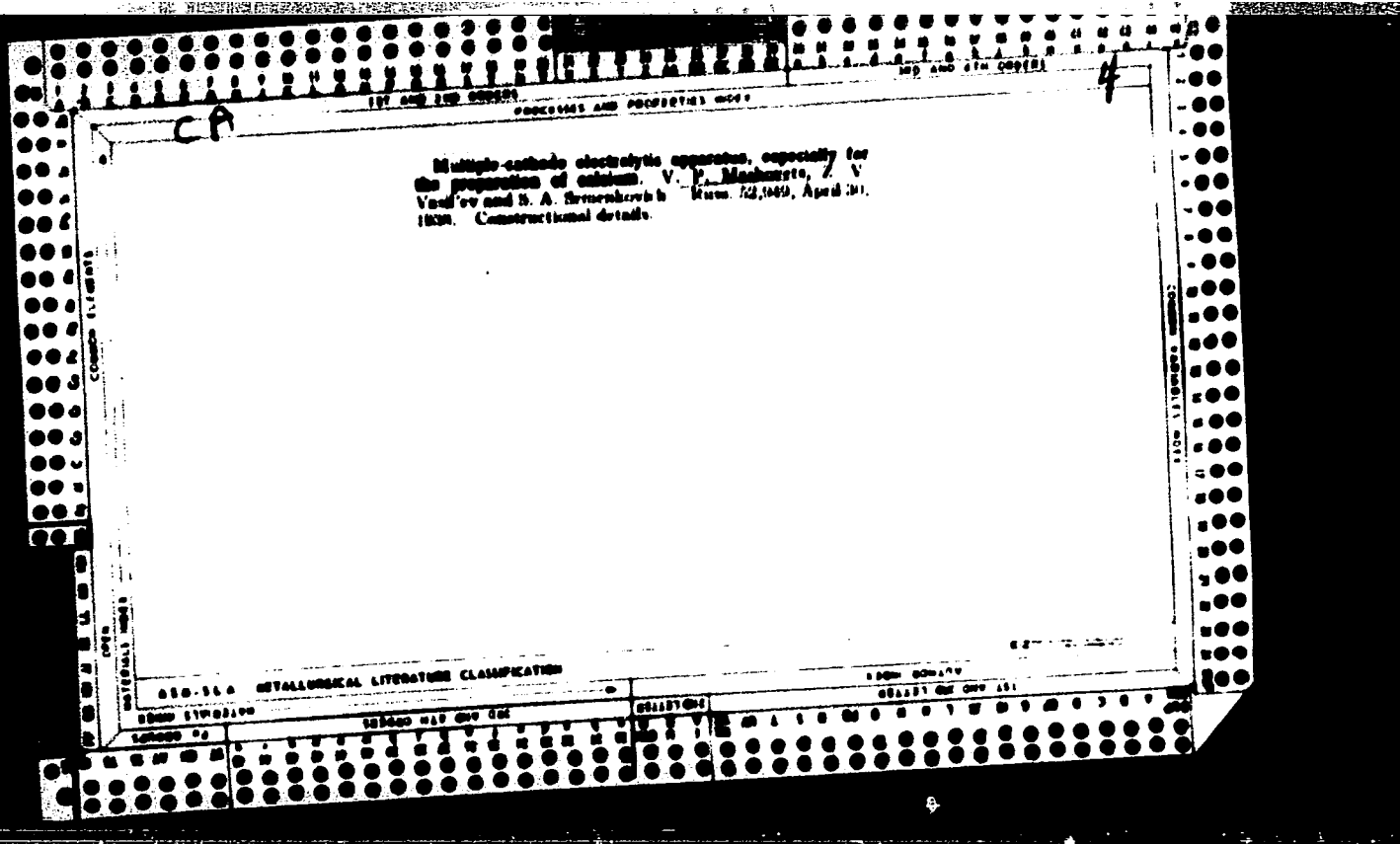
THE CHANGE IN THE MELTING POINT AND DEHYDRATION  
OF CRYOLITE WHEN FURNED IN AIR. W. P. Macfarlane (J. phys. Chem. 6, 601, 1902). The wide variations reported by different workers in the determination of the melting point of cryolite and cryolite-alumina mixtures are pointed out. It was found that, if fused cryolite is held for a prolonged period exposed to the atmosphere, the solidification temperature and the character of the solidification curve are both altered. Dehydration of the cryolite is due to the reaction with oxygen or water vapour in the air.

VS

1

THE MOLECULAR STATE OF THE OXIDE DERIVED IN  
CHRYSLER... Y. S. Shcherbakov (J. Soviet Chem. 6, 104, 1968). An equi-  
valent between carbon oxide, derived by carbon crystals, and the reaction  
products of this oxide with crystals (CaO, Al<sub>2</sub>O<sub>3</sub>, and Na<sub>2</sub>O) is found equal  
to unity. There is also an eq. between carbon oxide, taken as the  
standard, SiO<sub>2</sub>, and its reaction products with crystals, Al<sub>2</sub>O<sub>3</sub>, and  
Na<sub>2</sub>O.

1ST AND 2ND CROSS																				3RD AND 4TH CROSS																			
PROCESSOR AND PROPERTY INDEX																																							
<p><i>ca</i></p> <p>Formation of aluminum oxide during electrolysis of aluminum in fused crystals. Yu. V. Bolshakov, V. F. Mashovets and I. G. KH. <i>Lepko Metal.</i> No. 1, 23-6 (1967).—The e. m. f. of the <math>\text{Al} \text{Na}_2\text{AlF}_6 + 15\% \text{ AlCl}_3 \text{C}</math> cell is 0.88 v. at 1100° and 0.56 v. at 1100°. Al carbide is formed during electrolysis by an electrochem. reaction. M. W. Rasmussen</p>																																							
<p>ADDITIONAL METALLURGICAL LITERATURE CLASSIFICATION</p> <p>SEARCH SYMBOLS      CATALOGUE REFERENCE      ORIGINATOR      ANALYST OR USER</p>																																							



LIT. AND THE COVER		PROCESSING AND PROPERTIES INDEX		LIT. AND THE COVER	
<p><i>Calcium manufacture. V. P. Mashovets. Izvestiya Vuzov, No. 6, 1972, 8: Khim. <i>Prilozh.</i> 2, No. 5, 1972, 103-104. The main disadvantage in the production of Ca is its solubility in the electrolyte. This may be overcome by the use of a contact cathode. In the small single cathode baths (using water cooling) the cathode is of high and the cell impedance small. (Owing to the large amount of energy consumed (up to 10) kw.-hr./kg. Ca) and to the difficulties encountered in handling, the cost of Ca production increases. It is proposed to construct a multicathode bath without any artificial cooling which would permit the production of 1 kg. Ca per 20.5 kw.-hr. consumed.</i></p> <p style="text-align: right;">W. R. Hearn</p>					
<p>000-510 METALLURGICAL LITERATURE CLASSIFICATION</p>					
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**CA**

**PROCESSING AND PROPERTIES INDEX**

The resistance of aqueous electrolytes in relation to shape, dimensions and position of the electrodes. I. V. P. Mazurek and V. M. Borsukh, *Trudy Vsesoyuznogo Nauchno-Issled. Inst. 1960, No. 10, 180-180.*—Three equations for the calc. of the ohmic resistance of electrolytes confined between electrodes in the form of 2 coaxial cylinders are derived and equations detg. the dependence of resistance on lengths and radii of the electrodes are derived. Exptl. measurements on the electrolyte 0.1 N  $\text{CuSO}_4$  soln., with 2 Cu electrodes were made at 20° to confirm the theoretical results. The radii of the outer electrodes were 5 and 3.5 cm. and those of the inner electrodes 0.5, 1.5 and 3.5 cm. Two series of expts. were carried out: (1) with a const. length of the outer electrodes,  $h_2 = 6.2$  cm., the length of the inner electrode was varied from 1 to 15 cm. and (2) with a const. length of the inner electrode,  $h_1 = 6.2$  cm., the length of the outer electrode was varied from 1 to 6.2 cm. Results charted to exptl. data for the resistance are obtained from  $R = 0.1/\rho \cdot \rho[(h_2 - h_1) \log(h_2 r_2/h_1 r_1)] / [(h_2 r_2 - h_1 r_1) \log\{(h_2 - h_1 + \sqrt{(h_2 - h_1)^2 + (r_2 - r_1)^2}) / (r_2 - r_1)\}]$  ( $r_1$  and  $r_2$  are the radii of the inner and outer electrodes,  $h_1$  and  $h_2$  the lengths of the inner and outer electrodes and  $\rho$  is the resistivity of the electrolyte. A correction replacing  $h_1$  by  $h_1 - 0.25 r_1$  must be made for the inner electrode. II. V. M. Borsukh and V. P. Mazurek, *Ibid.* 380-6.—A method for calcg. the resistance of the electrolyte confined between 2 flat round electrodes with various diams. and placed in parallel on a common axis with various interpolar distances is described. Three equations for detg. the re-

distance of the active zone of the electrolyte are given. One of these equations  $R_1 = \rho l / \pi r_1 r_2$  ( $\rho$  is the resistivity of the electrolyte;  $l$  the interpolar distance,  $r_1$  and  $r_2$  are the radii of the electrodes) can be used for approx. calcg. Exptl. measurements of the resistances of 0.1 N and N  $\text{CuSO}_4$  solns. with Cu electrodes described indicate considerable deviations of the curves from those obtained from theoretical equations. The exptl. resistance curve becomes a straight line at certain small interpolar distances. The resistance values of the curvilinear part in some regions of the interpolar distance agree satisfactorily with those obtained from the equation  $R_2 = \rho l / \pi r_1 (r_2/l \sin \alpha)$  and the values of the linear part coincide with those obtained from the equation  $R_3 = [\rho / \pi r_1 r_2] \{h_1 + (r_2 - r_1)^2 / l \sin \alpha\}$ , where  $\alpha$  is the angle of the base of the truncated cone of the electrolyte zone which takes part in the transfer of the ions.  $l \sin \alpha$  depends on the relation between the radii of the electrodes and on the properties of the electrolyte.  $l \sin \alpha$  characterizes the degree of dispersion of the current in the electrolyte and is detd. empirically. Through  $K_{\text{Hou}}$ . *Referat. Zhur.* 1960, No. 6, 95. W. E. Henn

ASB-514 METALLURGICAL LITERATURE CLASSIFICATION

RESEARCH SYMBOL

UNCLASSIFIED

UNCLASSIFIED

RESEARCH SYMBOL

UNCLASSIFIED





MASHOVETS, V.P. - 1947, 1948.

№ 96 (Investigation of certain properties of storage-battery red lead oxide). Issledova-  
nie nekotorykh svoystv okislitsverga svinnogo.  
Zhurnal Prikladnoi Khimii, 20(3): 225-238, 1947.









MASHOVERS, V. P., L'KOMYAKOV, V. G. and KUZ'MIN, L. L.

"Technology of Electrochemical Production", Tekhnologiya Elektrokhimicheskikh  
Proizvodstv, Goskhimizdat, 676 pp, 1949.

MASHOVETS, V. P.

"Technology of the Electro-Chemical Industry," Moscow, 1949.

CA

4

The voltage balance of an electrolyzer. V. P. Maslovets  
and G. A. Forsblom. *Zhur. Priklad. Khim.* Applied  
Chem. 22, 1061 (1949). The conventional procedure of  
averaging the potential of an electrode and assuming an av-  
erage ohmic drop across the electrolyzer can be meaningless if the  
field between the electrodes is nonhomogeneous. Theo-  
retically and experimentally it is possible to have a field dis-  
tribution in which certain points of layers of the electrolyte  
lying at the anode are at a lower potential than some points  
close to the cathode. N. Thou



FDD PA 169T46

MASHOVETS, V. P.

Metals - Metallurgy, Lead Aug 30

"Method for Preparing Microsections of Lead and Its Alloys," V. P. Mashovets, A. X. Lyandres, State Sci Res Bat Inst

"Zavod Lab" Vol XVI, No 8, pp 1014-1016

Reviews existing methods and recommends method consisting of cutting specimens with microtome and of subsequent coarse etching and polishing and of subsequent coarse etching and polishing and of subsequent coarse etching and polishing and of subsequent coarse etching and polishing. Mixture of equal volumes of strong acetic acid and concentrated H peroxide has to be used for coarse etching. Reagent for fine

169T46

Metals - Metallurgy, Lead Aug 30  
(Contd)

etching consists of nitric acid, glacial acetic acid and glycerin in ratio of 1:1:2. Method permits discernment of separate structural components of alloys, and to expose orientation of crystals.

169T46

CA

4

A method of investigation of the electric field in solutions.  
V. P. Maslovskii. *J. Applied Chem. U.S.S.R.* 23, 63-78  
(1950) (Engl. translation).—See *C.A.* 44, 4802d.  
R. M. S.

Method of investigation of the electric field in solutions  
 (L. Mankusova, *Zhur. Priklad. Khim.* (1) Applied Chem.) 28, 66-80 (1955). — The potential distribution is detd. in a  $\text{CuSO}_4$  electrolyte soln. in a flat L-shaped cell made of a horizontal glass bottom, 2 vertical parallel L-shaped Cu strips serving as cathode and anode, and two end strips of glass. The distance between one pair of branches of the L-strip is 2 cm., between the other pair, 18 cm. Viewed vertically, the cell is a model of half a cell for Al electrolysis. The measurements, after passage of a polarizing current, give the potential distribution curves along consecutive sections of the cell, and hence permit construction of maps of isopotential and elec. field lines. These maps give the current distribution over the electrodes, the sp. elec. cond. of the soln., the spatial distribution of the ohmic and polarization energy, the elec. resistance of the cell, and the polarization curve. The method is applicable to models of electrolyzers of any prescribed shape.  
 N. Thon

MASHOVETS, V.P.; FORSBLOM, G.V. Prinimal uchastiye POPOV, R.B.;  
GULYANITSKIY, B.S., inzh., retsenzent; FIRSANOVA, L.A.,  
red.; ATTOPOVICH, M.K., tekhn. red.

[Electrolytic production of aluminum] Elektroliticheskoe  
proizvodstvo aliuminiia; prakticheskoe rukovodstvo dlia  
rabochikh, brigadirov i masterov tsekhev elektroliza aliu-  
minevykh zavodov. Moskva, Metallurgizdat, 1951. 220 p.  
(MIRA 16:7)

1. Vsesoyuznyy alyuminiyevo-magniyevyy institut (for  
Mashovets, Forsblom).

(Aluminum--Electrometallurgy)

MASHOVETS, V.P.; YUDIN, B.F.

Thermodynamics of the interaction between  $\text{AlF}_3$ ,  $\text{Na}_3\text{AlF}_6$  and  $\text{NaAlF}_4$   
with water vapor. Izv. vys. ucheb. zav.; tsvet. met. 5 no.4  
95-105 '62. (MIRA 16:5)

1. Leningradskiy tekhnologicheskoy institut, kafedra fizicheskoy  
khimii.

(Aluminum fluoride—Thermodynamic properties)  
(Cryolite—Thermodynamic properties)  
(Vapor pressure)

Electrochemistry-4

CA

Effect of the geometrical parameters of the electrolyser on the distribution of electrical energy within it. V. P. Mashovets, N. V. Pototskaya, N. L. Komarov, and U. P. Tiromshina. *Zhur. Priklad. Khim.* 24, 154-55; *J. Applied Chem. U.S.S.R.* 24, 100-90(1951) (Engl. translation); cf. *C.A.* 64, 6808d. — (in a model of a single-anode Al bath) the effects of varying the distance from the anode to the side wall, the depth of the electrolyte, and the interelectrode distance ( $L$ ) were studied by using an aq. soln. of  $\text{CuSO}_4$ ,  $\text{H}_2\text{SO}_4$ , and alc. at  $25^\circ$ . The fields were plotted (*loc. cit.*). The formula  $S_p = (A + 3L)(B + 3L)$ , where  $S_p$  is the derived cross section of the electrolyte and  $A$  and  $B$  are the length and width of the electrode, resp., is recommended for the design of Al baths. Earl S. McColliv

A-U Inst. Aluminum Magnesium

MASHOVETS, V. P.

2  
8/10/60

The effect of nonconducting inclusions on the conductance of an electrolyte. V. P. Mashovets. Zhur. Priklad. Khim. 24, 353-60. J. Appl. Chem. U.S.S.R. 24, 391-8 (1951) (Engl. translation).—Exptl. and graphic data are reported from a study of the effect of cylindrical and spherical nonconducting inclusions on the cond. of an electrolyte. An empirical formula  $K = (K_0/K_1) = 1 - \phi$  is offered for calcg. relative cond., and  $K_1 = 1 - 1.78\phi + \phi^2$  when  $K_0$  is the sp. cond. of the pure electrolyte,  $K_1$  is the sp. cond. of the electrolyte contg. inclusions, and  $\phi$  is the relative packing factor. The formula is claimed to hold good for all spherical inclusions and for packing factors that do not exceed 0.4 of the total vol. for cylindrical inclusions.

D. F. Brown

8-30-60

MASHOVETS, V. P.

Metallurgical Abst.  
June 1954  
Electrodeposition

③  
④  
The Rate of Growth of the System by the So-Called "Dispersibility" of Salts in Baths. V. P. Mashovets and G. V. Korobov (Zhur. Priklad. Khim., 1952, 25, (6), 532-533 (in Russian)). J. Appl. Chem. U.S.S.R., 1952, 25, (6), 537-538 (in English).—According to Lainer and Krasovskiy ("Fundamentals of Electroplating", Moscow, 1950), the dispersibility of the bath is the divergence of the distribution of the metal from the fundamental distribution of current, thus indicating the possibility of obtaining a uniform deposit on a profiled cathode without the use of contoured anodes, screens, etc. M. and F. propose analytical expressions enabling the effect on the dispersibility of variations in the polarizing powers of the electrodes, the sp. elect. conductivity of the electrolyte, the current strength, and the distance between the electrodes to be determined. By graphical construction of the elect. fields in various baths, it has been shown that a given variation in any one factor may lead to either more or less uniform distribution of the current on the cathode, depending on the geometrical parameters of the bath.—G. V. E. T.



ASHOVETS, V. P.

The role of geometrical factors in the so-called "non-uniformity" of galvanic baths. V. P. Ashovets and G. V. Pavlovskiy. *J. Appl. Chem. U.S.S.R.* 29: 807-808 (1955) (Engl. translation); *Zhur. Priklad. Khim.* 28: 532-53 (1955).—Analytical expressions are proposed for detg. the effect of variations in the polarizing power of the electrodes, sp. cond. of the electrolyte, current strength, and distance between the electrodes on the distribution of current on the cathode in relation to the geometrical parameters of the cell. By a series of graphs of the elec. fields in various cells, it was shown that one and the same variation of any one factor lead both to more uniform and less uniform distribution of current on the cathode, depending on the geometrical parameters of the cell. A systematic connection between the effect of the various factors and the geometrical parameters of the cell was shown. B. R.

MAKHOVETS, V. P.

232T40

UssR/Chemistry - Aluminum

809 52

"Investigation of the Composition of Anode Gases During the Electrolysis of Molten Cryolite-Alumina," V. P. Makhovets, M. F. Dogramadzhi, Ye. M. Merinskaya

"Zhur Prikl Khim" Vol 25, No 9, pp 955-965

Authors state that before this work, the formation of pure  $CO_2$  as a primary anode product had never been established experimentally in the electrolytic production of Al. A specially constructed laboratory bath set up for the electrolysis of molten cryolite-alumina permitted the generation of the primary anode gas, avoiding protected contact of the gas with the carbon anode. An increase in temp and a decrease in the anodic current enriched the primary gas with carbon monoxide. The content of CO was also increased by using a carbon anode with high oxidizability. By using low temp and high current densities, a primary gas consisting of almost pure carbon dioxide was generated. In industrial single-anode baths, the av content of  $CO_2$  in bath gases approached 55%-60%. The relation of the composition of anode gases to the above factors was confirmed, as well as to the width of the anode and to the time of taking the sample. At the time of the anode effect, a significant amt of gas of unknown compn with a high mol wt was found.

(3)

232T40

MASHOVETS, V. M.

7  
An investigation of the composition of anode gases during electrolysis of cryolite-alumina melt. ~~by V. M. Mashovets, M. P. Dzyuravskaya, and E. M. Tikhonova. Zh. Prikl. Khim.~~ *Chem. U.S.S.R.* 25, 1023-30 (1952); *Eng. Printed. Russ.* 25, 956-65 (1952).—A large-scale lab. cell was constructed of such design to allow the immediate sampling of primary anode gas. Increase in temp. and decrease in c.d. enriched the anode gas with CO. CO increased with readily oxidizable C anodes. Low temp. and high c.d. with low-activity C anodes gave 97% CO<sub>2</sub> in the anode gases. CO<sub>2</sub> (65-80%) was found in anode gas from industrial uni-anode cells.  
Charles M. Mason

my

MASHOVETS, V.P.

✓ Evaluation of voltage drop in aluminum cells. G. V. Forshman and V. P. Mashovets (All-Union Aluminum-Magnesium Inst., Leningrad, *Zhur. Priklad. Khim.* 25, // 1163-76 (1962); *Ch. C.A.* 46, 4802a. The ohmic voltage drop  $\Delta V$  in a cryolite- $\text{Al}_2\text{O}_3$  bath with Al and graphite electrodes was detd. analytically as a function of parameters obtained either from a plot of the elec. field or from the dimensions of the electrodes, length  $A$  and width  $B$  ( $P = 2(A + B)$ ) and the interelectrode distance  $L$ . At first it was assumed that the entire polarization effect was due to that of the graphite electrode. Then 3 fields of this electrode were plotted: no assumed polarization; polarization assumed according to the c.d. vs.  $\eta$  data of Karpacheva, *et al.* (*C.A.* 43, 6519a) and according to similar data of de-Kay Thompson, *et al.* (*C.A.* 27, 4483). The analysis of these fields led to the conclusion that the effect of polarization on  $\Delta V$  was negligible and the equation was reduced to

$$\Delta V = (I\rho/N^2) \sum_{i=1}^{i=N} m_i = 1.56$$

which was considered in satisfactory agreement with exptl. data ( $I = iN$ ,  $i$  the elec. power of each "tube" of force,  $N$  the no. of tubes in the entire vol.,  $m$  the no. of elements of vol. in each tube, and  $\rho$  the specific resistance of the electrolyte). A simpler equation which could be solved without plotting the electrode field was obtained: From previously published data (*C.A.* 46, 10962g) it was shown that the effect of the distance  $C$  between the walls and the edges of the electrodes was negligible for  $C \geq 5L$ . It was also shown that for  $L$  between 3 and 10 cm. the no. of tubes as a function of  $L$  was practically linear. Within these limits of  $C$  and  $L$  the equation was  $\Delta V = I\rho L/[AB + P(L + 2.5)]$ . Over a wide range of the parameters the calcd. values agreed satisfactorily with exptl. data. I. Benicowitz

1. MASHOVETS, V. P.: FORSBLOM, G. V.
2. USSR (600)
4. Electric Currents
7. Distribution of a direct current electric field in electrolyzers. Zhur. fiz. khim. 26 no. 10, 1952.

9. Monthly List of Russian Accessions, Library of Congress, March 1953. Unclassified.

MASHOVETS, V. P.

✓ Influence of the Geometric Parameters of the Electrolytic Cell on the Distribution of Potential and Current on the Electrode Surface. G. V. Forsblom and V. P. Mashovets (Trudy Sovetskoye po Elektrokhimii 1950, 1953, 431-441). (In Russian). Various experiments were made, using acid  $\text{CuSO}_4$  baths. The effective electrode potential, calculated for the mean c.d., depends on the geometry of the cell. The ohmic resistance of the electrolyte depends not only on the geometry and the resistivity of the electrolyte, but also on the polarizability of the electrode and the current strength, so that the conception of a "cell const." is meaningless. The same is true of the idea of "throwing power". —(V. E. T.)

MASHOVETS, V P

NG The Effect of Temperature on Mould Filling in the Casting of Lead-Antimony Alloys. V. P. Mashovets and E. I. Deragan. Soviet Metallurgy (Moscow: Prosvetlennost, 1986, (No. 14-21). [In Russian]. A special test was used to study the effect of mould and metal temp. on the fluidity of 4 alloys contg. resp. Sb 3-8, 8-12, 8, and 12%, remainder Pb. The test mould was made in cast Fe and contained 8 vertical pyramidal cavities (from 1 to 8 mm. sq. at the base and 40-100 mm. long) all joined to a common gating system. The degree of filling of the moulds was used as an index of the fluidity of the alloy. The results show that the poorest fluidity is obtained with the alloy contg. Sb 8-12% and that the mould temp. can be better utilized to control the fluidity than can the metal temp. —Y. K.

① - 2/2/87

"APPROVED FOR RELEASE: 07/12/2001

CIA-RDP86-00513R001032720009-7

MASHOVE 13, V. P.

APPROVED FOR RELEASE: 07/12/2001

CIA-RDP86-00513R001032720009-7"



MASHOVETS, V.P., prof., doktor tekhn. nauk.

Investigating copper oxide cells at low temperatures. Soor. nanch.  
trad. LITIZHT no.5:214-221 '53. (MIRA 11:3)  
(Electric batteries)

MASHOVETS, V.P.

USSR

Checking the discharge of copper oxide cells by the specific gravity of the electrolyte. V. P. Mashovets, *Sbornik Nauch. Trudov Leningrad. Elektrolit. Inst. Inzhenerov Zhelazo-Dorozh. Transporta*, 1953, No. 6, 222-1; *Koleral. Khim.*, 1954, No. 34787. The condition of CuO cells could be checked from the sp. gr. of the electrolyte (KOH soln.) which changed because of the accumulation of zincate according to  $\text{CuO} + \text{Zn} + 2\text{KOH} \rightarrow \text{Cu} + \text{K}_2\text{ZnO}_2 + \text{H}_2\text{O}$ . There was no appreciable layer sepn. in the electrolyte and the change of its d. could be expressed by  $d_s = d_0 + ak + bk^2$ , where  $k$  was the capacity in fractions of the nominal taken as 1,  $d_0$  was the initial d.,  $d_s$  was the final d., and  $a$  and  $b$  were coeffs. 0.144 and 0.03, resp. When the cell was discharged, zincate crystd. out and the d. of the electrolyte became const. The check could be carried out with an ordinary storage-cell pipet hydrometer.

M. Hosen

✓Concerning the Criterion for the Uniformity of Distribution of a Metal on the Cathode. V. P. Maslovets (*Zhur. Priklad. Khim.*, 1953, 28, (7), 775-778; *U.S.S.R.*, 1953, 28, (7), 731-735 (in English)). Although emphasizing the desirability of obtaining such a criterion, M. criticizes the papers and books of Kadanev (preceding abstract) on this subject. The criterion  $M_1/(M_1 + M_2)$  would be more suitable than  $M_1/M_2$ . The phys. meanings of  $M_1/M_2$  and  $m/dl$  are different. The former criterion characterizes the uniformity of distribution of the metal. The meaning of the latter quantity is best given by considering its reciprocal (with a negative sign prefixed); this signifies the relative change in the increase in weight of the deposit (or thickness or rate of deposition) with change of distance, and has no phys. meaning for a bath of arbitrary configuration. Throwing power is not an objective property of the electrolyte independent of the geometrical configuration of the bath. Apart from his other mistakes, K.'s derivations are all useless in that they are based on the fundamentally erroneous concept of rectilinear distribution of current. —G. V. E. T.

USSR .

The dependence of the electrochemical and ohmic fall of  
potential upon the geometry in an electrolytic cell (G. V.  
Forshlom and V. P. Mashovets. *J. Appl. Chem. U.S.S.R.*  
26, 113-8 (1953) (English transl.).—See C.I. 48, 5688c.  
H. L. H.

MASHOVETS V.P.

The dependence of the electrochemical and ohmic fall of potential upon the geometry in an electrolytic cell. G. V. Forshlom and V. P. Mashovets, *Zhur. Priklad. Khim.* 26, 1020-5 (1953). The effective potential of an electrode was dependent upon local c. ds. which were detd. by cell geometry. In regions of low c.d., the electrode potential usually diminished faster than linearly with a decrease of c.d. Therefore the effective potential was lowered as current distribution became nonhomogeneous. The change in potential was illustrated for 2 electrolytic cells differing only in the shape of the anode. A graphical method of field construction was used (C.A. 47, 9825c). Potential and current distribution patterns were shown for a cell with two parallel plate electrodes (presumably Cu) 300 mm. long, sepd. by a distance,  $l$ , where  $l = 50$  or 100 mm. One electrode was displaced 100 mm. relative to the other. The technique permitted calcn. of cell consts. as used in cond. measurements (C.A. 44, 4802e). Cell consts.,  $C$ , were measured for a soln. contg. 50 g./l. of  $\text{CuSO}_4 \cdot 5\text{H}_2\text{O}$  and 3 solns. of the same concn. of  $\text{CuSO}_4$  contg.  $\text{H}_2\text{SO}_4$ . At  $l = C = 2.05$  for the  $\text{CuSO}_4$  soln.; 2.32 for a soln. contg. 20 g./l.; 2.33 for a soln. contg. 60 g./l.; and 2.09 for a soln. contg. 350 g./l. At  $l = 50$  mm., with a.c.,  $C = 1.33$  for all 4 solns.; with d.c. (45 ma.),  $C = 1.33$  for the  $\text{CuSO}_4$  soln.; 1.40 for the soln. contg. 20 g./l.; 1.60 for the soln. contg. 60 g./l.; and 1.80 for a soln. contg. 350 g./l. With the soln. contg. 50 g./l. and  $l = 50$  m.m. the values of  $C$  at 15 and 90 ma. d.c. were 1.68 and 1.40, resp. The increase of  $C$  in the d.-c. measurements with higher  $\text{H}_2\text{SO}_4$  concns. resulted from longer current lines and must be ascribed to greater polarization since the cond. increased. Current distribution must be uniform to obtain reproducible electrolytic cell data, especially in good conductors such as fused salts. For this reason, "cell consts." derived from a.-c. data were inadmissible for use in d.-c. electrolysis.

R. D. Allen

A-11 Aluminium Magnesium Inst.

FRUMKIN, A.N., akademik; FORSBLUM, G.V.; MASHOVETS, V.P.

Conditions for the modeling of the electric field of electrolyzers. Dokl.  
AN SSSR 91 no.3:593-595 J1 '53. (MLRA 6:7)

1. Vsesoyuznyy alyuminiyevy-magniyevyy institut (for Forsblom and Mashovets).
2. Akademiya nauk SSSR (for Frumkin).  
(Electrolysis--Electromechanical analogies)

MASHOVETS, V. P.

The Committee on Stalin Prizes (of the Council of Ministers USSR) in the fields of science and inventions announces that the following scientific works, popular scientific books, and textbooks have been submitted for competition for Stalin Prizes for the years 1952 and 1953. (Sovetskaya Kultura, Moscow, No. 22-40, 20 Feb - 3 Apr 1954)

<u>Name</u>	<u>Title of Work</u>	<u>Nominated by</u>
Mashovets, V. P. Foreblom, G. V.	"Investigation of DC Electrical Fields in Electrolyzers"	State Scientific Research Institute of Aluminum and Magnesium (13)

80: W-30604, 7 July 1954

MASHOVETS V.P.

(2)

Distribution of the electric field of direct-current cells.  
V. P. Mashovets and G. V. Roshkov. *Zhur. Priklad.*  
*Khim.* 17, 280-87 (1964); cf. *C.A.* 47, 7919h. To con-  
firm experimentally the differential equations and conclu-  
sions derived analytically and previously reported, the equi-  
potential lines of a rectangular electrolyzer were detd. over  
a wide range of c.d., polarizing power of the electrodes  
(Cu, Pb), and the sp. cond.  $\kappa$  of the electrolyte. Electro-  
des of identical dimensions and parallel to each other  
were offset so that only a part of each was opposite the  
other, thus distorting the field. The electrolytic contact  
was so mounted that it could be moved normal and parallel  
to the electrodes. The potentiometer was set at predetd.  
p. d.  $\Delta U$  and the contact moved over the cell until the zero  
point was reached and recorded. At the end of the expt.  
the entire cell was plotted with equipotential lines. The  
current lines, normal to the equipotential lines and forming  
angle  $\theta$  with the electrode, were drawn with a divider so that  
the distance between them was equal to that between the  
equipotential lines. The no. of spaces, "tubes of force,"  
between the current lines,  $n$ , in the field and their current  
force,  $i$ , entered in all subsequent calcs.:  $\kappa = I/1.5n\Delta U$ ,  
where  $I = ia$ , ( $1.5 \text{ cm.} =$  the electrolytic depth in the cell).  
The calcd. and exptl. values of  $\kappa$  agreed within  $\pm 5\%$ .  
Curves of c.d. vs.  $y$  yielded the values of  $d\eta/dj$ , the polarizing  
power of the electrodes, and those of c.d. vs.  $\lambda$  gave  $dj/d\lambda$ ;  
 $j =$  the c.d. over the electrode and  $\lambda$  the distance in cm. of a  
given point from the edge (left) of the electrode. The  
calcd. value of  $\tan \theta = -j/\kappa(d\eta/dj)(dj/d\lambda)$  agreed satis-  
factorily with the exptl. values, considering the difficulties  
of obtaining the several values from plots. Addnl. con-  
clusions made previously (loc. cit. and *J.A.* 48, 6885i) were  
corroborated.  
I. Bencowitz

*[Handwritten signature]*  
12/16/64



*MASHOVETS, V.P.*  
BELETSKIY, M.S.; MASHOVETS, V.P.

Determining the amount of aluminum in an electrolytic cell  
by means of radioactive tracers. TSvet.met. 28 no.5:51-54  
S-O '55. (MIRA 10:10)  
(Aluminum--Analysis) (Radioactive tracers)

*Mashovets, V. P.*

Category: USSR/Analytical Chemistry - Analysis of inorganic substances.

G-2

Abs Jour: Referat Zhur-Khimiya, No 9, 1957, 31040

Author : Mashovets V. P., Zakharov Ye. L.

Inst : not given

Title : Analytic Determination of Carbon Fluorides in Anodic Gases of an Aluminum Cell

Orig Pub: Zh. prikl. khimii, 1956, 29, No 10, 1512-1521

Abstract: The method of determination of carbon fluorides in the gases is based on decomposition of the fluorides with water vapor in the presence of activated  $Al_2O_3$  and  $SiO_2$  (at  $700-800^\circ$ ) followed by absorption of  $CO_2$ ; CO is burned over CuO at  $300-350^\circ$  and the resulting  $CO_2$  is absorbed in alkaline solution of pyrogallol. The method is applicable in the separation of CF from higher fluorides. The method described is more sensitive and yield better reproducible results than the fluoride method. It was found that anodic gases of an Al-cell having fired anodes, do

Card : 1/2

-59-

Analysis of carbon fluoride  
aluminum bath

9  
4E2c  
4E41

MASHOVETS, V.P., doktor tekhnicheskikh nauk, professor; RAMLAU, A.I.,  
assistant, inzhener; SUPRUN, L.M., assistant, inzhener.

Electrode potentials of copper oxide electrode elements and testing  
the discharge duration pattern. Sber.LIIZHT no.151:222-237 '56.  
(Electrodes) (MLRA 10:1)

MASHOVETS, V.P., ~~доктор технических наук~~, professor.

Stabilizing battery galvanic cell voltage. Sbor. LIIZHT no. 151: 238-  
246 '56. (MLRA 10:1)

(Electric batteries)

AUTHOR: Mashovets, V.P., Professor.

136-5-10/14

TITLE: The heat balance and calculation of inter-electrode distance for aluminium electrolyzers. (O teplovom balanse i raschete mezhduelektrodnogo rasstoyaniya alyuminievykh elektrolizerov.)

PERIODICAL: "Tsvetnye Metally" (Non-ferrous Metals) 1957, No.5, pp. 63 - 69 (U.S.S.R.)

ABSTRACT: The author deplores the complications which have been introduced into heat-balance and electrode-separation calculations for aluminium electrolyzers. For example, P.P.Fedotov (1) started the unnecessary practice of referring heat-balances to the electrolyzer temperature. This has led to numerous errors and some confusion (refs. 2,3,4), which have been criticised by I.M. Kaganskii and A.A. Edingaryan (5). The main cause of this unfortunate development is attributable to the unjustified use of the second law of thermo-dynamics for problems completely covered by the first law. The author favours 0 °C as the reference in temperature, in agreement with G.A. Abramov and his co-workers (7) and Kaganskii and Edingaryan, and cites the balance published by V.D.Ponomarev and I.Z. Slutskii (8) as an example of confusion and error partly due to the use of another temperature. In discussing

Card 1/2

The heat balance and calculation of inter-electrode distance for aluminium electrolyzers. (Cont.) 136-5-10/14

the thermo-dynamics of electrolyzer operation, the author mentions his own experimental work with A.A. Revazyan (11) and his criticism together with G.V. Forsblom (13) of the views of G.A. Abramov et al. (7). G.V. Forsblom's (17) relatively high value (0.63-0.83 cm) is attributed to gas saturation and foaming, K.P. Batashov (16) having obtained lower values. For calculating inter-electrode distance it is only necessary to know the reversible decomposition voltage and the over-voltage in the given concrete conditions of the electrolyzer, and the requirements enumerated by B.S. Gulyanitskiy and V.V. Krivoruchenko (18) are considered to be incorrect.

There are 18 references, 14 of which are Slavic.

ASSOCIATION: All-Union Aluminium-magnesium Institute (VAMI)

AVAILABLE:

Card 2/2

MASHCHETS, Y. P.

Electromotive force of galvanic cells of fused cryolite. Mashchets, Y. P., Mashcheta and A. A. Kevgevan. Zhur. Priklad. Khim., 30, 1009-12 (1967). The e.m.f. of cells  $\text{Al}|\text{NaAlF}_6 + \text{Al}_2\text{O}_3||\text{gas electrode}$  were found at 1000-113°; the gas electrodes were:  $\text{Pt}(\text{O})$  and  $\text{Pt}(\text{O}_2)$  (I),  $\text{Pt}(\text{CO}_2)$  (II),  $\text{C}(\text{CO}_2)$  (III), and  $\text{C}(\text{O})$  (IV). The electrolytic cells consisted of 2 concentric porous sintered aluminum cylinders inside a graphite crucible. The inside cylinder protected the gas electrode from possible "metallic fog." The Mo wire connecting the Al electrode and the C gas electrodes (hollow C tubes) were protected by corundum sleeves and so was the Pt electrode with the gas flowing through the tube. Synthetic cryolite ( $\text{NaF}:\text{AlF}_3 = 3$ ) was used with  $\text{Al}_2\text{O}_3$ . The theoretical e.m.f. of I (2.12 v.), calcul. from the free energy of the reaction  $\text{Al}_2\text{O}_3 \rightarrow 2\text{Al} + 1.5 \text{O}_2$ , indicated that the reaction was reversible. The exptl. e.m.f. of a gas contg. 12.8%  $\text{O}_2$  and 87.1%  $\text{N}_2$  was 2.09-2.01, and that of a gas contg. 8.5%  $\text{O}_2$  and 91.5%  $\text{N}_2$  was 1.84-1.83 v. The O electrode approached reversibility at  $\text{O}_2 = 1 \text{ atm.}$  so that the process was more accurately represented by  $\text{Al} \rightarrow \text{Al}^{+++} + 3e$  on the anode and  $\text{O}_2 + 4e \rightarrow 2\text{O}^{--}$  or  $\text{O}_2 + 2\text{Al}_2\text{O}_3 + 4e \rightarrow 4\text{AlO}_2^{--}$  (depending on the character of the O contg. anion) on the cathode and  $2\text{Al}^{+++} + 3\text{O}^{--} \rightleftharpoons \text{Al}_2\text{O}_3$  or  $\text{Al}^{+++} + 3\text{AlO}_2^{--} \rightleftharpoons 2\text{Al}_2\text{O}_3$  in the liquid phase. The e.m.f. of II was equal to the theoretical value, 1.10-1.12 v., and the process was represented by  $\text{CO}_2 + 4e \rightarrow \text{C} + 2\text{O}^{--}$  or  $\text{CO}_2 + 2\text{Al}_2\text{O}_3 + 4e \rightarrow \text{C} + 4\text{AlO}_2^{--}$ . The e.m.f. of III decreased with time from 1.346-1.40 v. during the first 5 min. to 1.11 v. after 30 min. and remained const. at this value till the end of the expt. (120 min.). The C electrode had not been treated in any way except that it was held over the



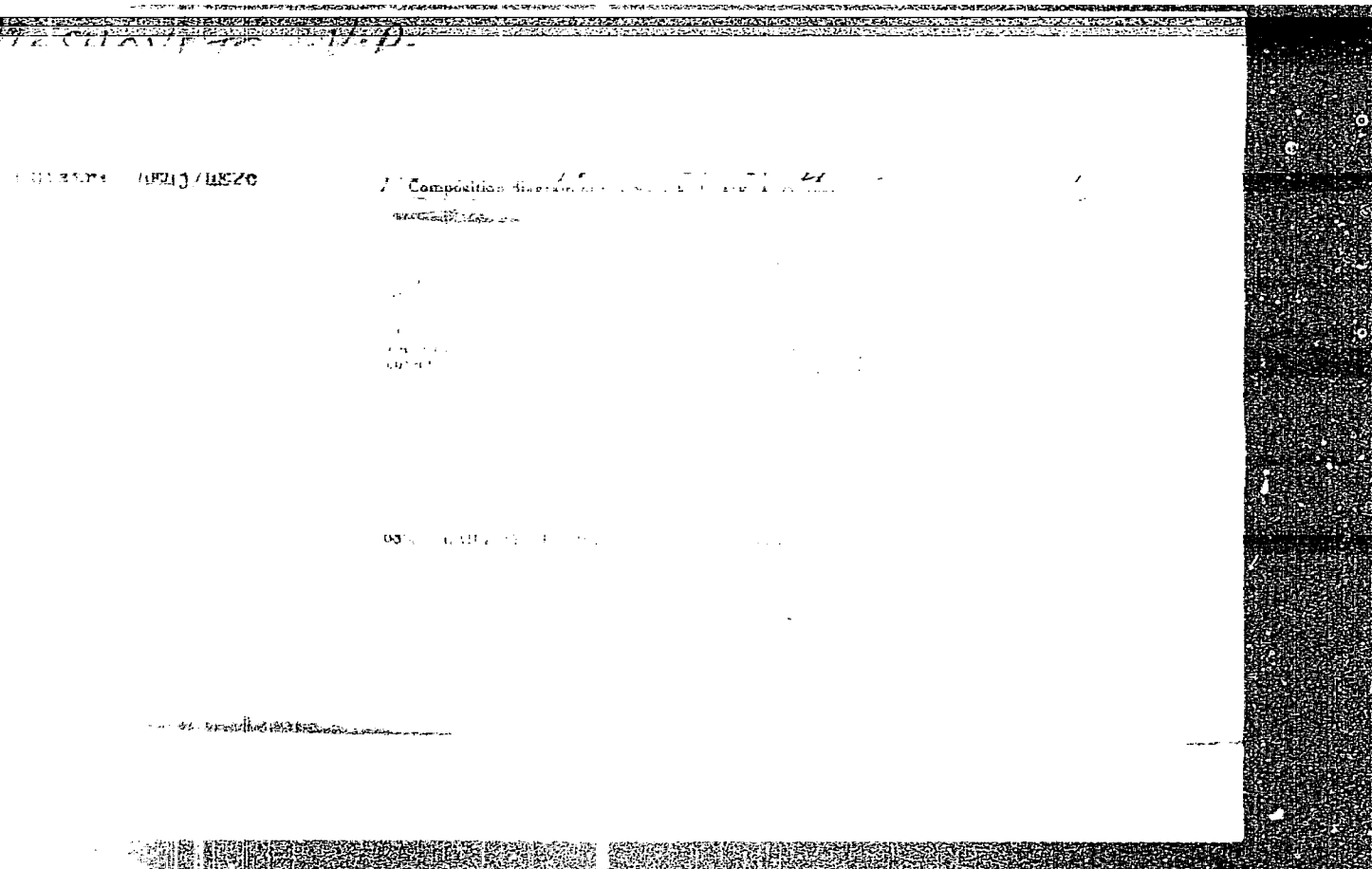
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mele for 15-20 min. before submerging. In 1 expt. the  $\text{CO}_2$  was stopped after the const. e.m.f. (1.11 v.) was reached, and the e.m.f. decreased to 0.74 v. In another expt. the C electrode was removed and kept in the air a few min. and then submerged; the initial e.m.f. was 1.35-1.45 v. A similar decrease of the e.m.f. with time was exhibited by electrode IV. These results indicated that  $\text{CO}_2$  was the controlling factor and that an intermediate gas  $\text{C}_2\text{O}$  was formed.

I. Rencowitz

DM RF

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MASHOVETS, V. P.

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AUTHOR: ~~Mashovets, V. P.~~

TITLE: On the Cathodic Process in the Electrolytic Manufacture of Aluminum (O katodnom protsesse pri elektroliticheskom poluchenii alyuminiya)

PERIODICAL: Tr. Vses. alyumin. -magn. in-ta, 1957, Nr 39, pp 274-287

ABSTRACT: A majority of the authors who have investigated the relationship existing between the current efficiency and various factors in the course of electrolysis of melts have arrived at the following empirical formula:  $\eta = 1 - k/j^n$ , where  $\eta$  is the current efficiency,  $k$  is the losses of substance (or of electrical energy),  $j$  is the current density, and  $n$  is an exponent. The value of the constant  $k$  in the aboveindicated formula is determined empirically and is a function of temperature, interelectrode spacing, design of the electrolyzer, composition of electrolyte, etc. It represents the relative losses in metal (the fraction of metal lost) at  $j = 1 \text{ amp/cm}^2$  and is always less than unity. The values of the exponent  $n$  vary among different authors from 0.5 to 1.0.

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On the Cathodic Process in the Electrolytic Manufacture of Aluminum

possible to determine correctly in principle metal losses that are independent of the electric current. However, a comparative analysis of the equations presented has shown that a universal equation should cover not only the chemical losses, which are independent of the electric current, but also electrochemical losses which are a function of the electrode potential; these factors are not taken into account in the formulas presented above.

I. G.

1. Aluminum--Production    2. Aluminum--Electrolysis    3. Electrolysis  
--Applications

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